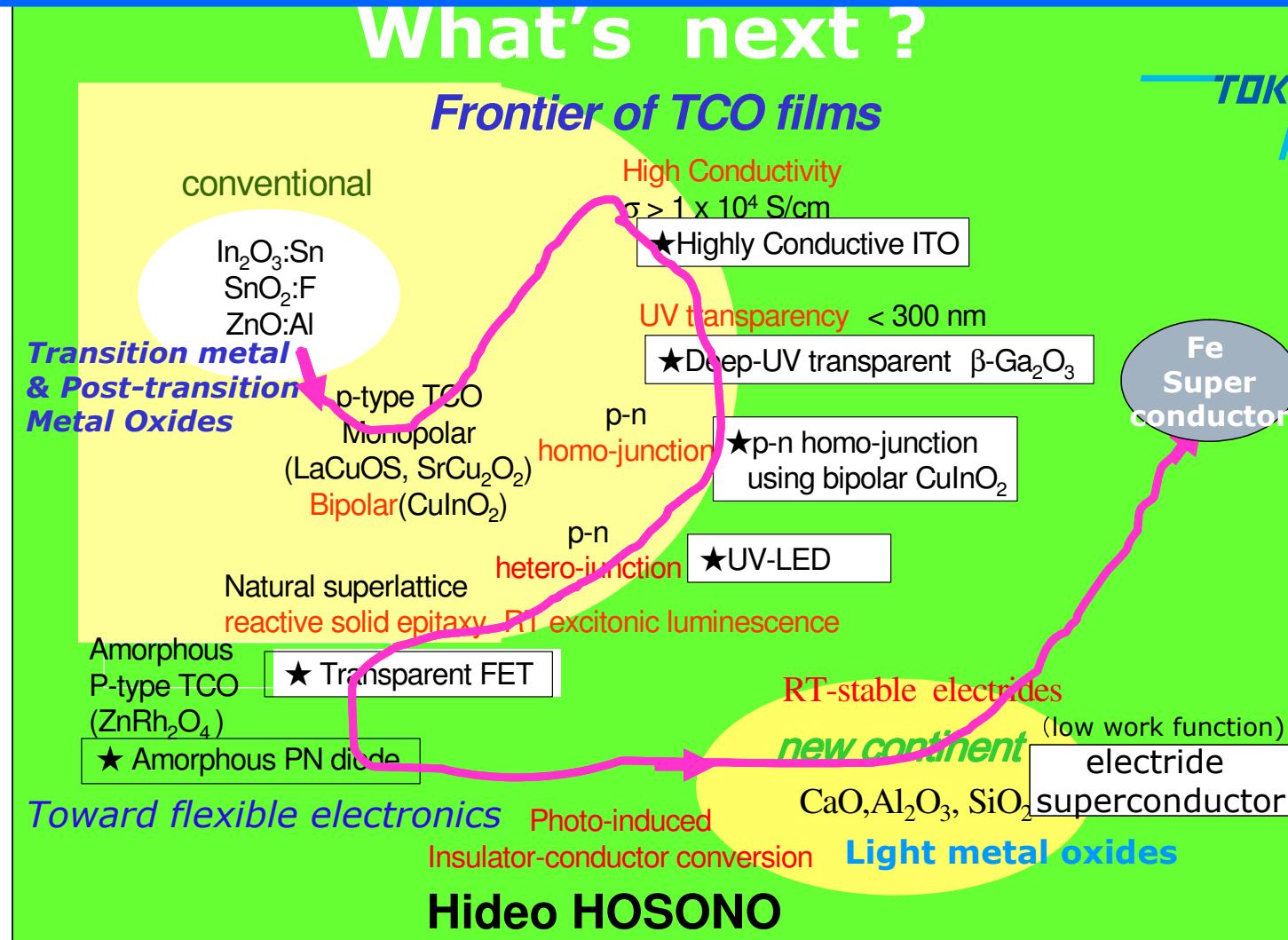


A New Continent of High Tc Superconductors: Layered Iron Pnictides

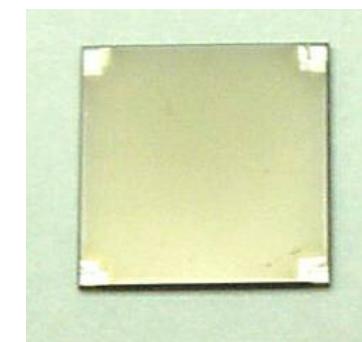
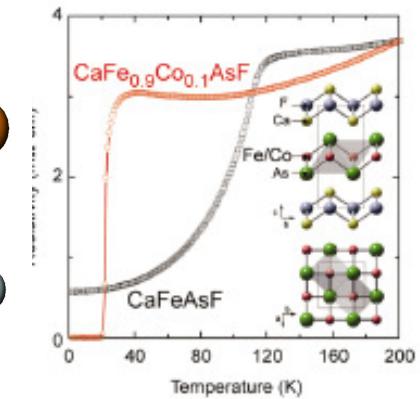
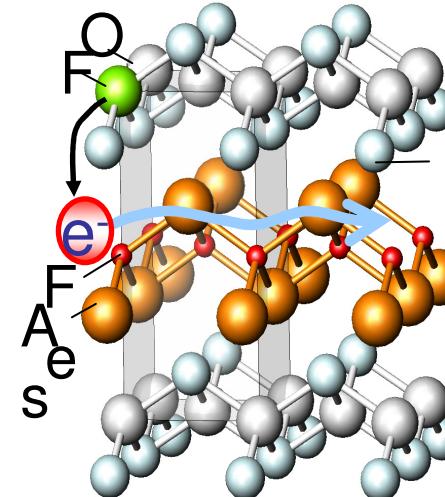
What's next ?



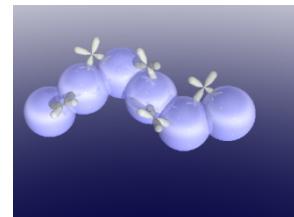
Frontier Research Center & Materials and Structures Lab.
Tokyo Institute of Technology, JAPAN

OUTLINE

- Background
- Discovery of Fe(Ni)-pnictide superconductor
- Requirement for High T_c
- Ca(Sr)FeAsF, new insulating layer
- Epitaxial Thin Film Growth
- Water vapor-induced superconductivity
- Perspective



3大素材(鉄、セメント、ガラス)から生まれた電子機能材料



透明アモルファス酸化物
半導体の提案(1995)

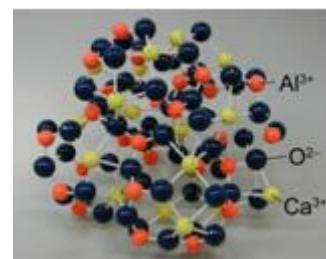
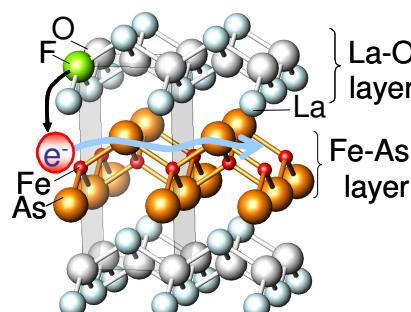


透明トランジスタの試作
(2004, Nature)

ガラスから高性能透明トランジスタ

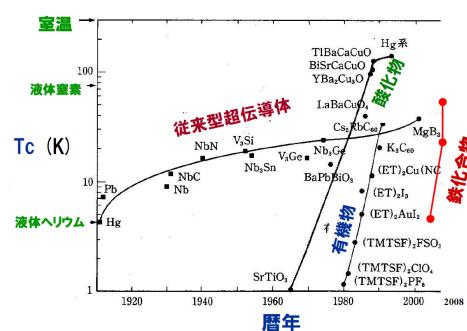


12インチ有機ELディスプレイ
の駆動に応用(2008, サムスン)



C12A7のナノ構造に注目
(1999)

鉄の化合物は超電導に
ならないという常識を破る
(2006)



セメントから透明金属



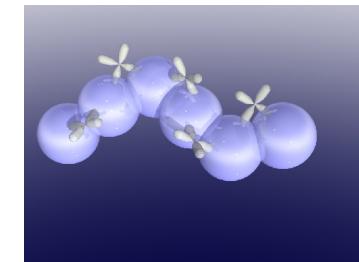
透明金属に変身。ITO代替物質。
(2004年 Science)

20年ぶりの高温超電導物質の発見
銅酸化物を除くと最高のTCを実現。世界的ブーム
(2008年, Nature)

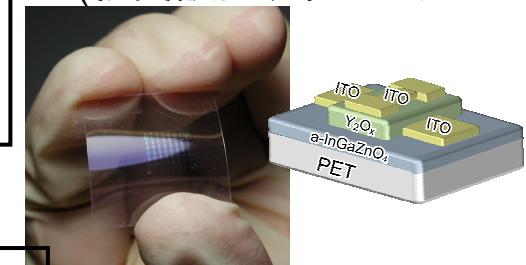
透明アモルファス酸化物半導体(TAOS)の提案と進展

細野グループ

- 1995 透明アモルファス酸化物半導体の提案 @ICANS-16
- 1996 透明N型物質探索指針 (*J. Non-Cryst. Sol.*)
- 2002 特徴的電子輸送特性の解明 (*Phys. Rev. B*)
- 2003 P型物質の発見とPN接合ダイオードの室温形成 (*Adv. Materials*)
- 2004 酸化物半導体単結晶薄膜を用いた高性能透明トランジス(*Science*)
- 2004 AOSを用いた曲がる高性能トランジスタ(*Nature*)
- 2008 世界初のPチャネル酸化物TFT(*Appl. Phys. Lett.*)



(物質設計、東工大)



(透明で曲がるTFT, 東工大)

- 2005.9 アモルファス酸化物半導体(AOS) がメイントピックスとして採用@ICAN21(2005.9)
- 2005.12 10 papers @ MRS(ボストン)
- 2006.4 キヤノン スパッターで高性能TAOS-TFTを発表 @E-MRS(ニース)
- 2006.12 凸版印刷、新型電子ペーパを提案@IDW(大津)
- 2007.5 透明酸化物半導体TFT@SID(カリフォルニア)
- 2007.8 AOSが全論文の15%に@ICANS22(コロラド)
- 2007.8 Samsung,LG がOLEDを試作発表@IMIS(韓国)
- 2008.5 サムソン電子AOS-TFT駆動12インチOLED,15インチLCD発表 @SID(US)
- 2008.12 日立 TAOS-TFTで1.5V動作を実現、フレキシブル・デバイスに道 @国際電子デバイス会議(IEDM)



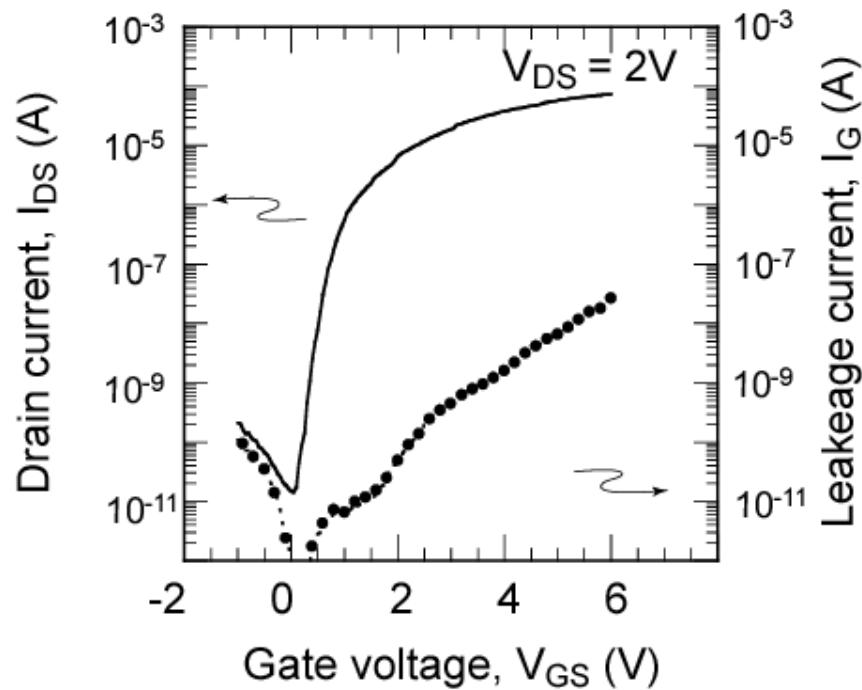
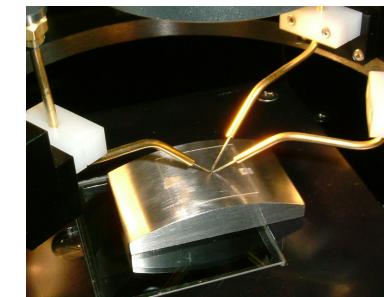
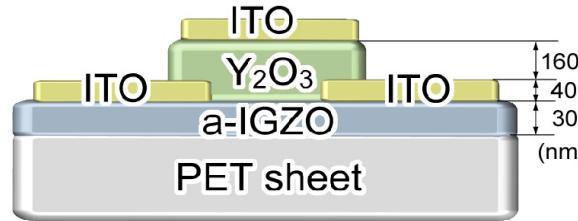
(電子ペーパ、凸版印刷)



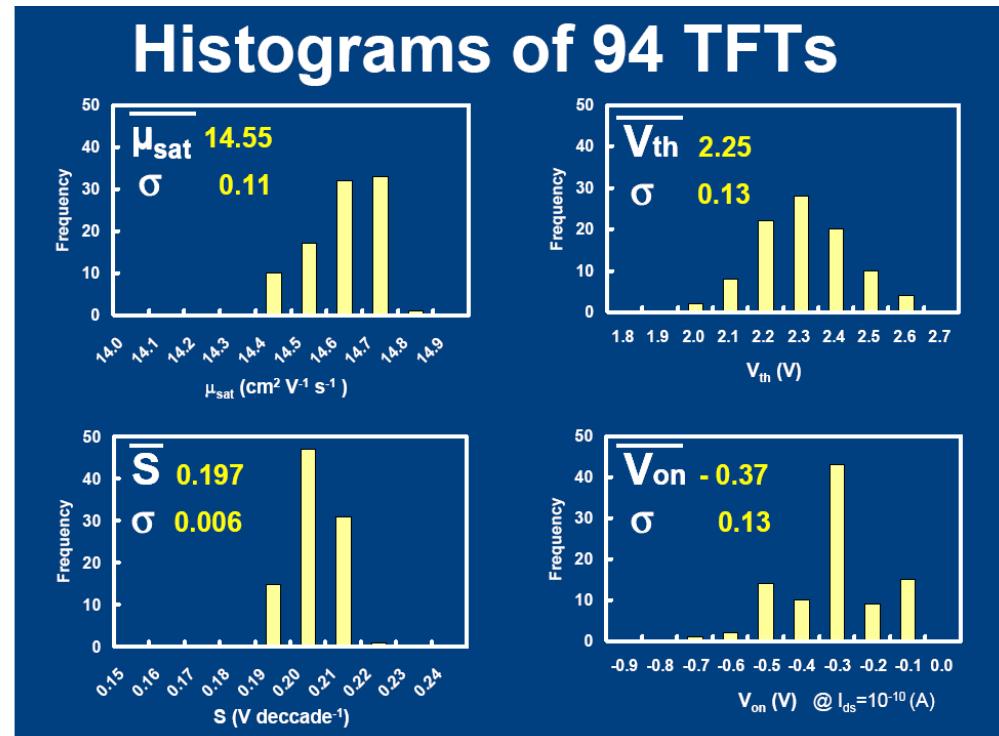
(有機EL,LG電子)

室温でPETフィルム上に作製した薄膜トランジスタ

電界効果移動度 μ
 $= 12 \text{ cm}^2(\text{Vs})^{-1}$



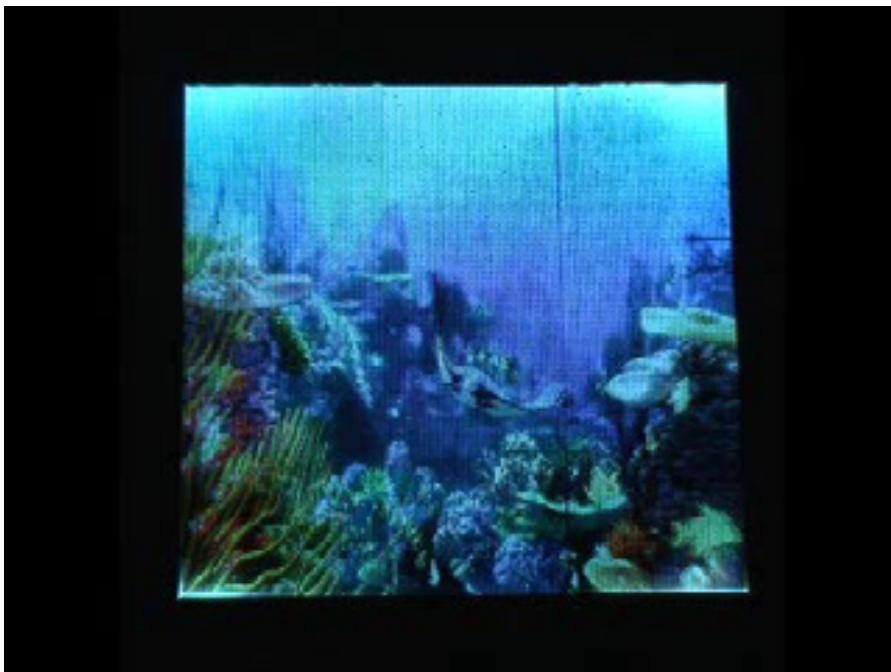
Cf. 水素化アモルファスシリコン
 $\mu \sim 1 \text{ cm}^2(\text{Vs})^{-1}$



Display Application

Full Color Image
Driven by TAOS - TFTs

4-inch



AM-OLED Panel

12-inch



LG Electronics @SID'07

Samsung Electronics @SID'08

SID 2009

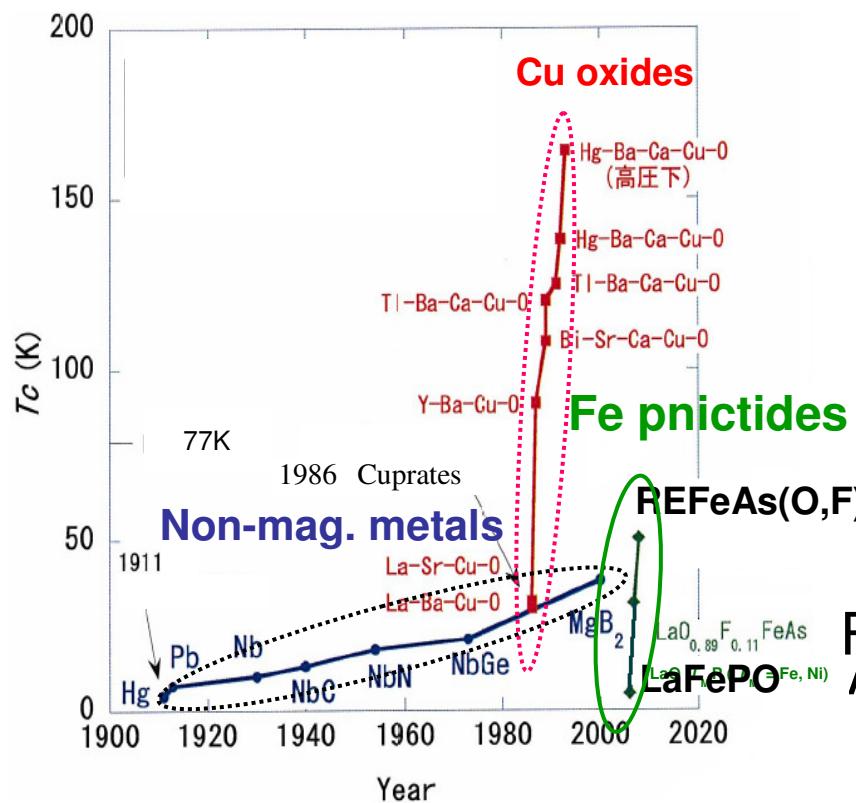
Solution-derived TFT



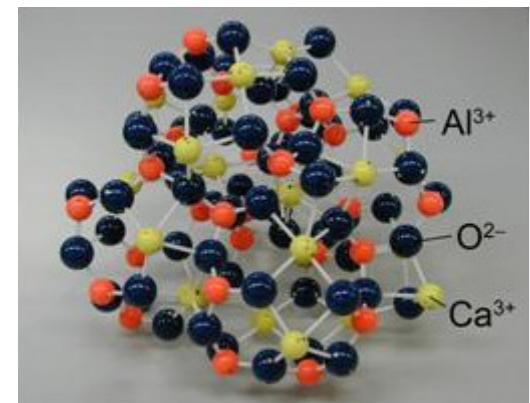
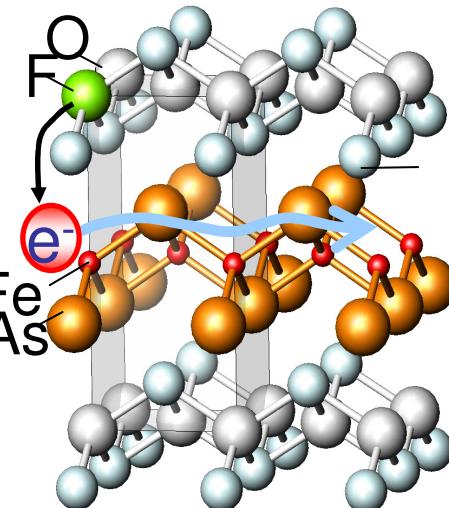
Trend in Superconductor Research

Bronze(Cu) age ➔ Iron age

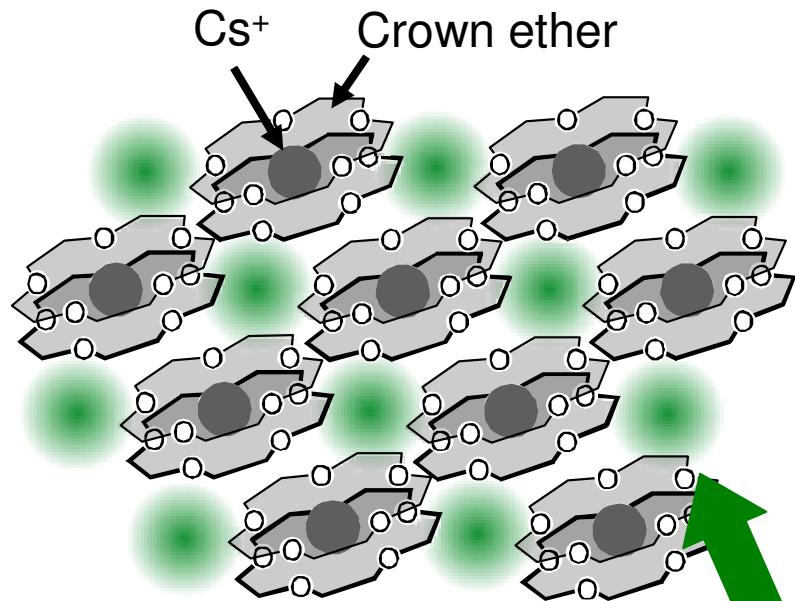
Stone age



Superconducting Cement

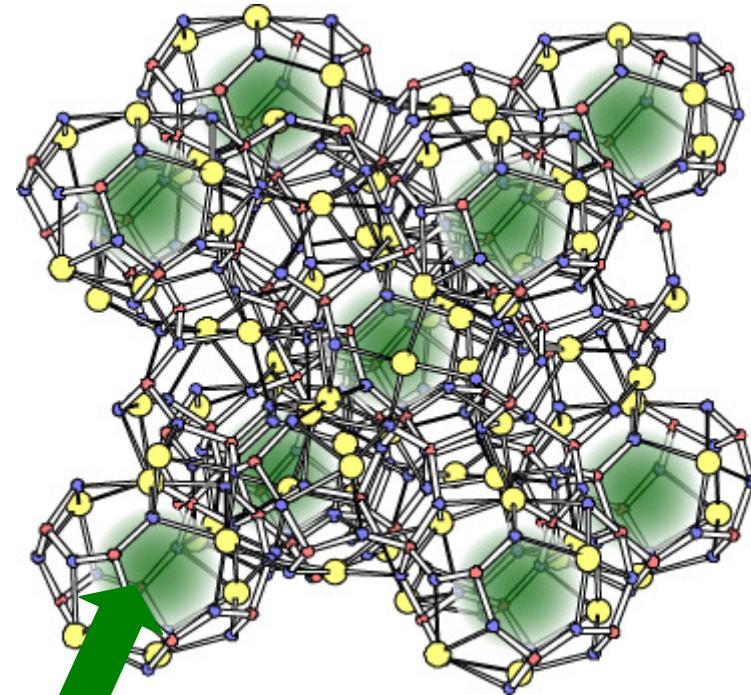


C12A7 electride



1983 ~ Dr. J. L. Dye
(Nature)

- Stable condition
max -40 °C in vacuum



2003 Matsuishi et al.
(Science)

- Stable condition
Up to ~ 400 °C in Air
Up to melting point (~1300°C) in vacuum

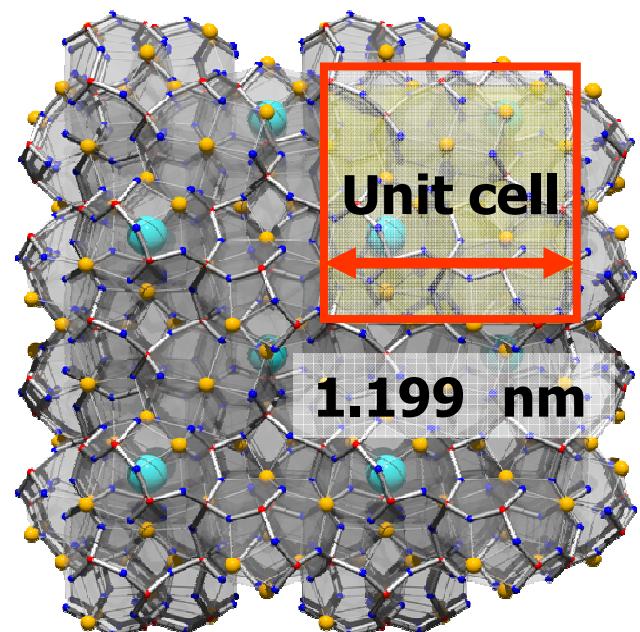
C12A7 electride is thermally and chemically stable

$12\text{CaO}\cdot 7\text{Al}_2\text{O}_3$ (C12A7)

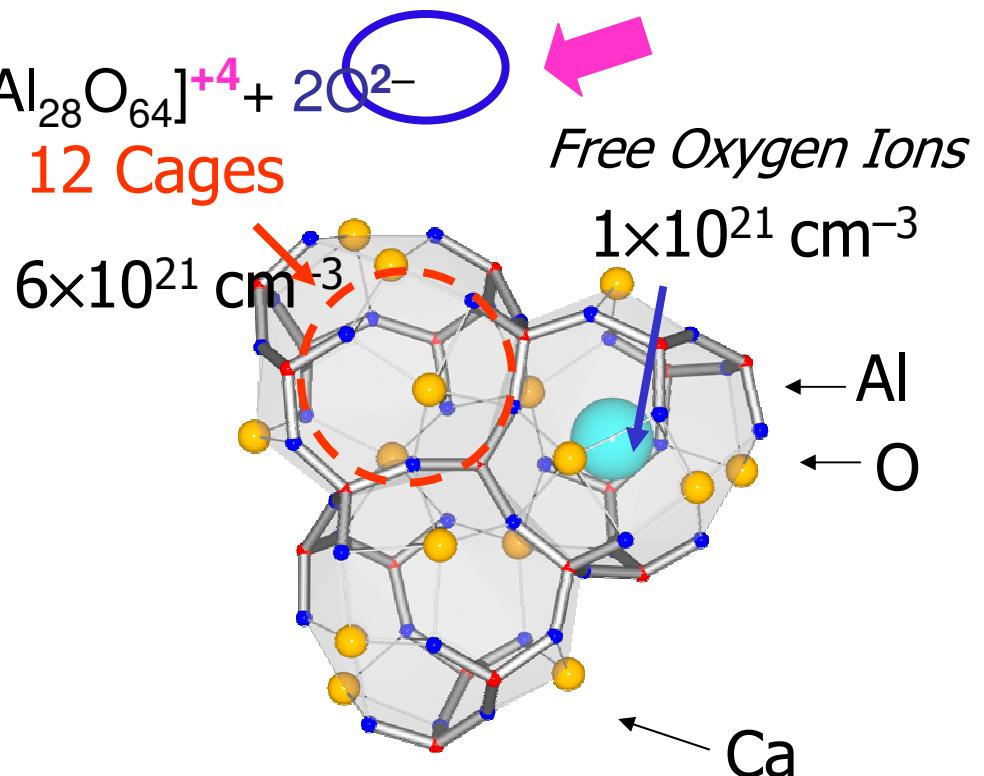


- A constituent of alumina cements
- Large band gap ~7 eV
- Cubic ($a = 1.199 \text{ nm}$, $\text{I}43d$)
- Unit cell: $\text{Ca}_{24}\text{Al}_{28}\text{O}_{66} = [\text{Ca}_{24}\text{Al}_{28}\text{O}_{64}]^{+4} + 2\text{O}^{2-}$

Mp. 1415°C



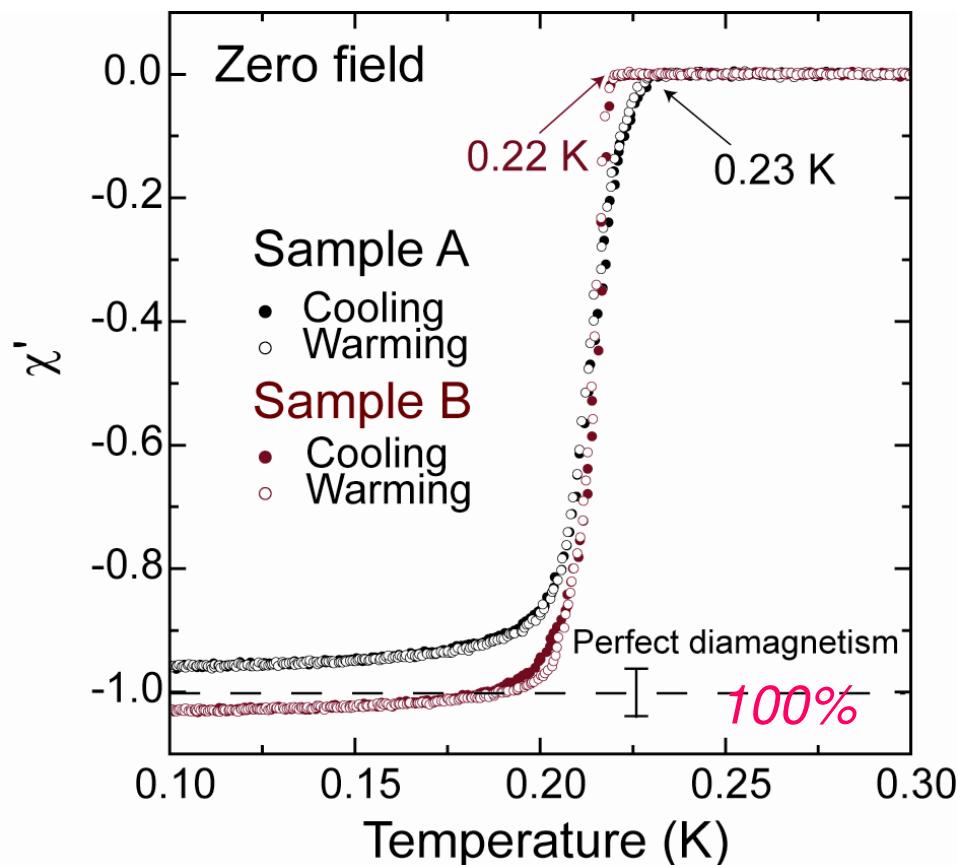
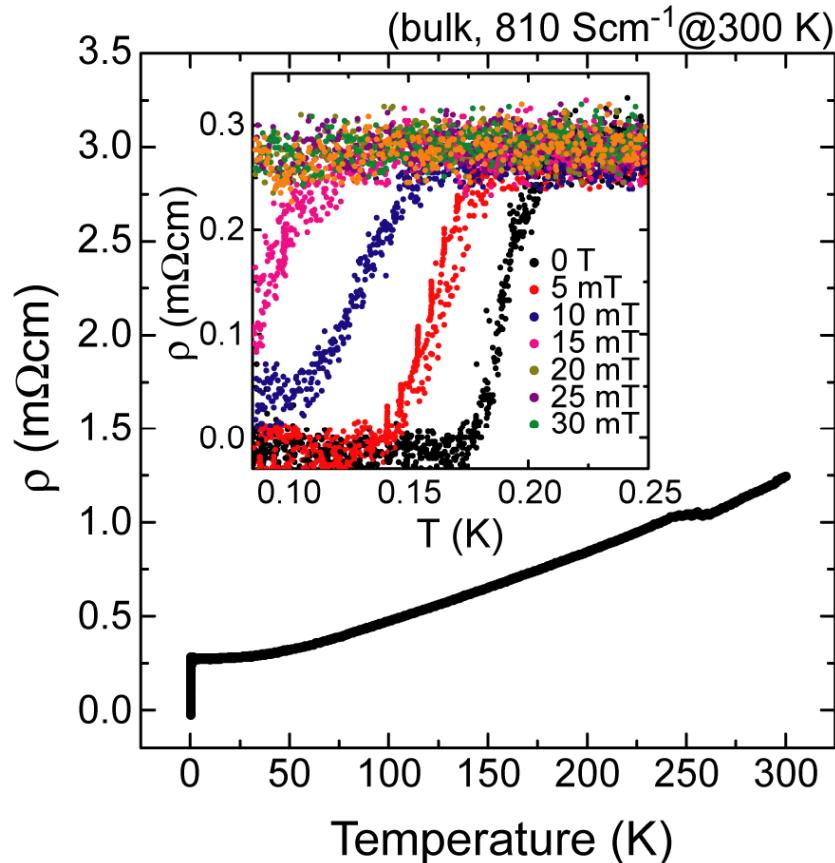
Densely Packed
Sub-nano-sized Cages



Fast Oxygen Ion Conductor

Metal-Superconducting Transition

Superconducting Cement



First *s*-metal superconductor

J.Am.Chem.Soc.(2007)

Superconducting cement: *beyond imagination?*

Vol 444 | 23 November 2006

nature

NEWS & VIEWS

SOLID-STATE PHYSICS

Super silicon

Robert J. Cava

Silicon is the archetypal semiconductor, and base material of the microelectronic age. But it turns out that, treated the right way, silicon the semiconductor can become silicon the superconductor.

If someone were to stop me in the street and ask me to name the most important materials on Earth, I would say concrete, steel, glass and silicon. To witness the importance of the first three, just look up from your page or screen. For the last, close your eyes and imagine yourself back in the BS (before-silicon) world of, say, Myrna Loy in *The Thin Man* or Humphrey Bogart in *Casablanca*. One might reasonably argue a preference for the softer focus of those earlier times; but the differences in lifestyle between then and now make it hard to argue against the assertion that silicon has become the technologically most important material of the past 50 years.

It is for this reason that Bustarret and colleagues' report (page 465 of this issue)¹ is such a breakthrough: they have succeeded in turning silicon, the consummate semiconductor, into a superconductor at ambient pressure. Admittedly, the treatment they meted out to silicon to force its conversion ('doping' with high levels of boron) can only be termed abusive, and the temperature at which they measured it (0.3



NEWS & VIEWS

Performing experiments using such high-powered lasers, and testing materials for superconductivity at such low temperatures, is no small matter. So why bother? The authors are motivated by the possibility that, if silicon could be made superconducting — even under conditions too extreme to be useful in practical devices — the integration of superconducting silicon into the sophisticated world of microelectronics processing might uncover new electronic functions. It will be interesting, for example, to see whether an electron-rich superconductor can be made out of silicon through extreme doping with electron-rich phosphorus or arsenic, rather than hole-rich boron. That would allow the gamut of microelectronics concepts and processing to be applied to superconductors, but is far from an obvious extension of the present work.

So, are Bustarret and colleagues' results² just an amusing diversion in the search for new superconductors, or a herald of more and better devices and materials? It's too early to tell. The main thrusts in the search for new

superconducting materials nowadays are towards exotic systems in which magnetism can be transformed into superconductivity by changing a carefully controlled experimental parameter, and towards materials based on metallic elements that have high superconducting transition temperatures and are easy to process. Such a material could change the way electrical current is carried. I remain convinced that we could wake up one morning to the announcement that someone, somewhere, has found it. If that superconductor is made by doping concrete, I'll know it's time for me to retire.

Robert J. Cava is in the Department of Chemistry, Princeton University, Princeton, New Jersey 08544, USA.
e-mail: rj.cava@princeton.edu

1. Bustarret, E. et al. *Nature* **444**, 465–468 (2006).
2. Lee, P. A. & Ramakrishnan, T. V. *Rev. Mod. Phys.* **57**, 277–325 (1985).
3. Thorne, G. A. *Phys. Rev. B* **2**, 470–484 (1970).
4. Rostoker, T. F. et al. *Phys. Rev. Lett.* **45**, 4723–4726 (1980).
5. Dai, P., Zeng, Y. & Suenaga, M. *J. Phys. Rev. Lett.* **65**, 1914–1916 (1990).

any two randomly chosen genomes than suggested previously by studying SNPs alone. More than half of the CNVs that were identified overlap known annotated genes in the genome. So it is likely that CNVs play a role in so-called complex diseases, in which multiple genes and/or gene-environment interactions are involved.

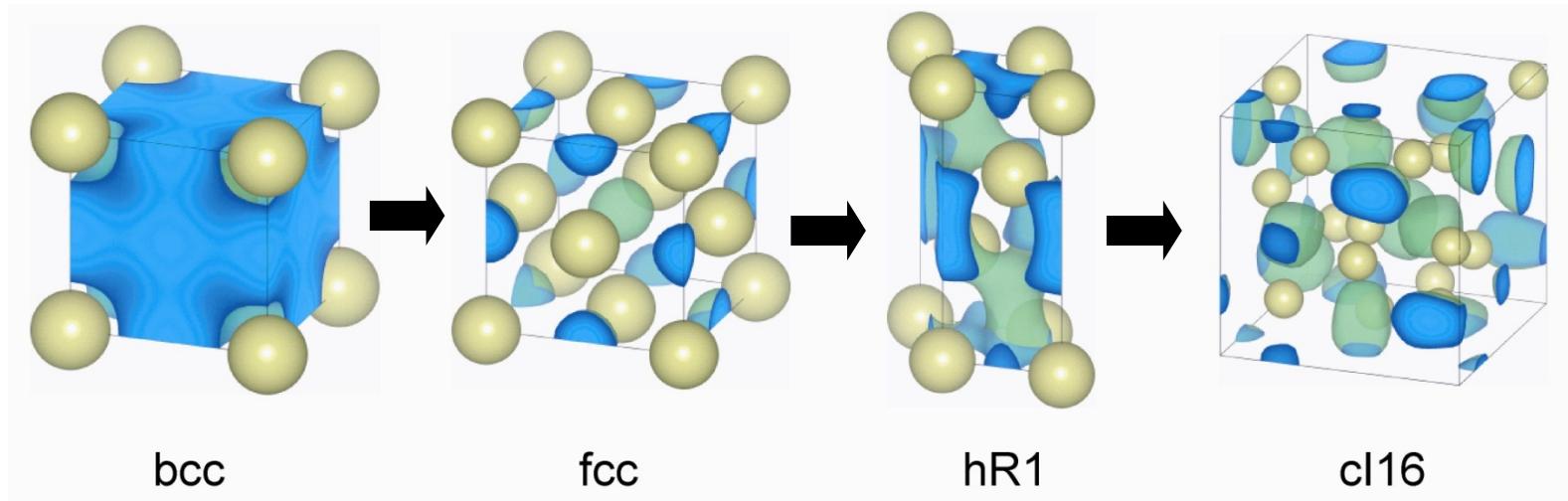
Mechanistically, how might copy-number variation be involved with complex disease? When deletions or duplications are present within a gene or its regulatory region, there is a reasonable chance that there will be an imbalance in the appropriate level of RNA and thus protein production from that gene. For genes and pathways in which the amount of a functional product produced is critical, it seems likely that CNVs could underscore variation in susceptibility to disease. Classically, variation in the copy number of the globin genes was shown to be responsible for various disorders of haemoglobin, such as the α -thalassæmias⁶. More recently, variable copy number of the *CCL3L1* gene was reported to be

Nature, Nov. 27, 2006

**If that superconductor is made by *doping concrete*, I'll know it's time for me to retire
(Robert J. Cava, Princeton U.)**

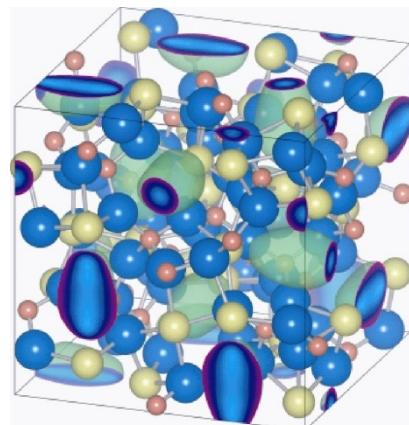
High P-phase of s-band metals and C12A7:e⁻

Pressure-driven Li phase



Metallic C12A7:e⁻

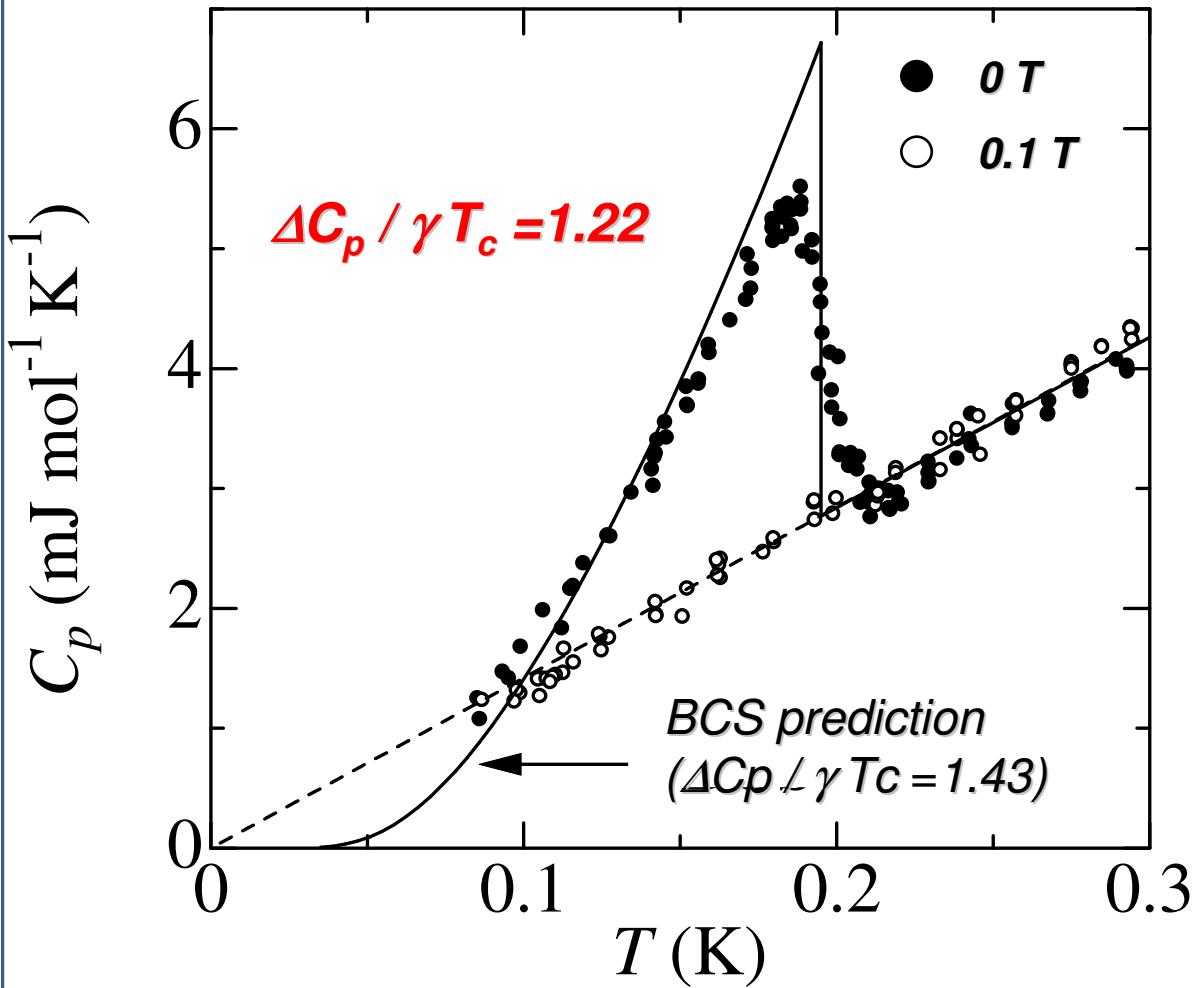
(Superconductor
 $T_c=20K$ @ High P)



*The Same Space Group
(Id3-4)!!!*

Heat Capacity

Sample ; FZ grown single crystal



$$C_p = \beta T^3 + \gamma T,$$

$$\gamma = \frac{1}{3} \pi^2 k_B^2 N_\gamma(0),$$

$$\Theta_D = \left(\frac{12\pi^4 Rr}{5\beta} \right)^{1/3},$$

$$N_\gamma(0) = 7.0 \times 10^{21} \text{ eV}^{-1} \text{ cm}^{-3}$$

$$\Theta_D = 628K$$

(C12A7:O²⁻ ; 604K)

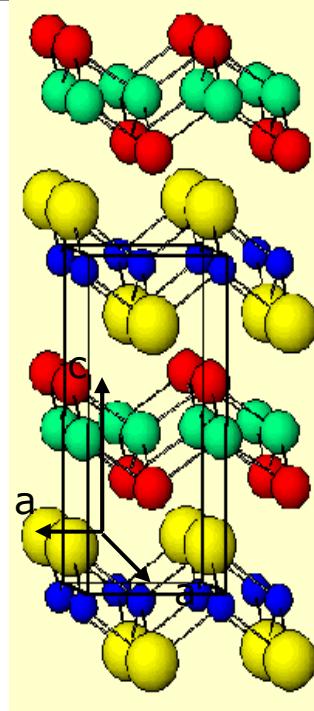
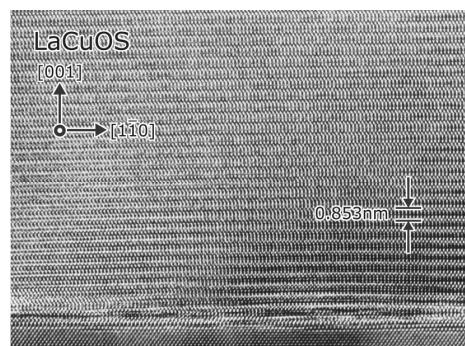
Unique Optoelectric Properties of **LaCuOCh(Ch=S,Se)**

- ## Transparent p-type degenerate semicon.

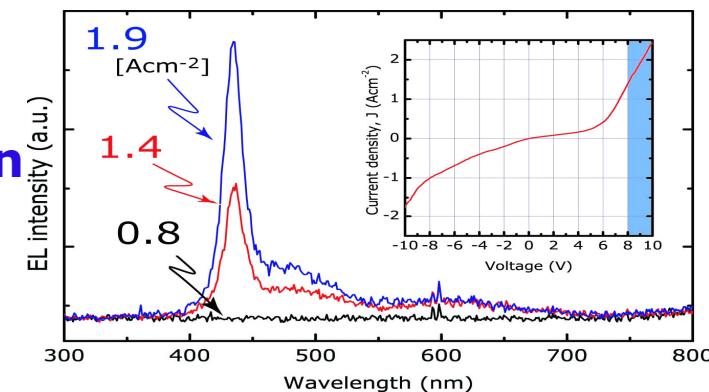
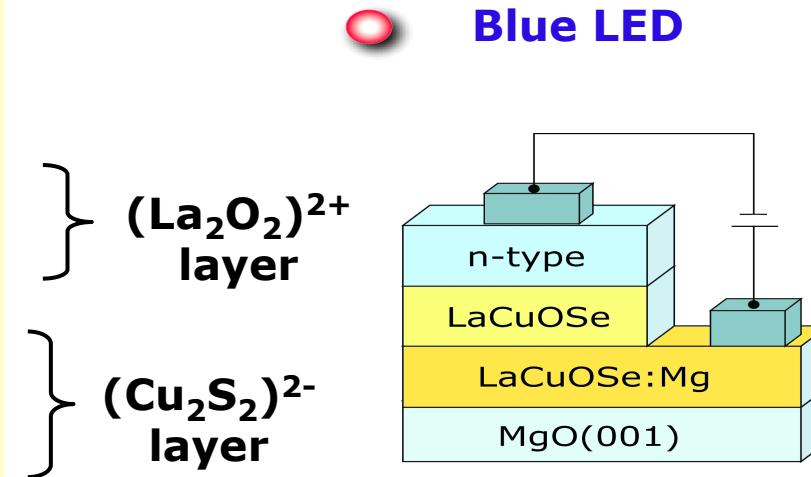
The diagram illustrates the concept of modulation doping. A central 'Well' layer, labeled 'CuCh', contains Mg dopants. This well is sandwiched between two 'Barrier' layers, each labeled 'La O'. Red arrows point from the barrier layers towards the well, indicating the diffusion of Mg dopants into the central layer.

$$N = 4 \times 10^{20} \text{ cm}^{-3}$$

$$\sigma = 140 \text{ Scm}^{-1}$$

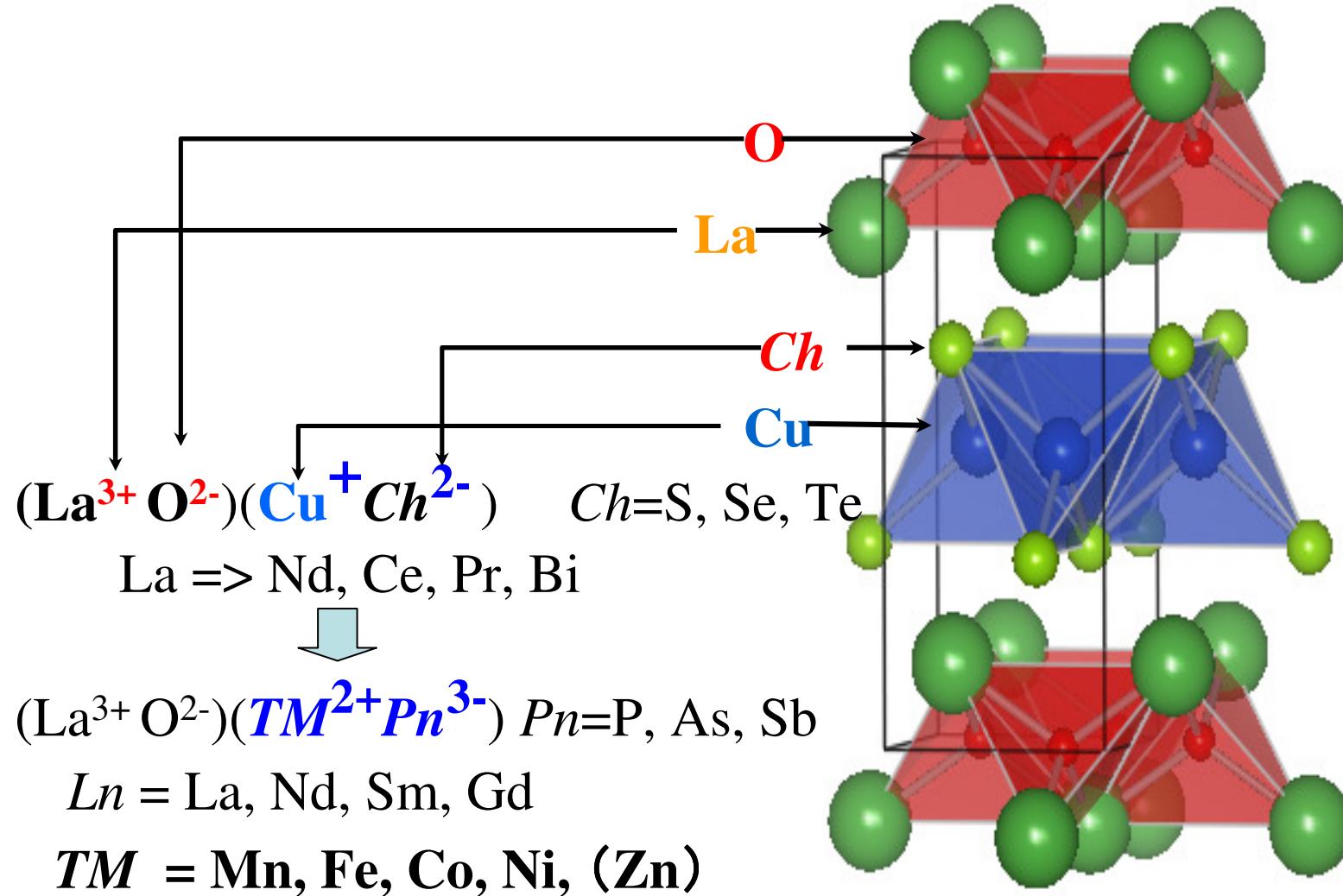


- RT-stable exciton
 - Large NLO



APL(2002), PRB(2003), OPL(2003), APL(2005)

From LaCuOCh (p-type semicond.) to LaTMOPn (magnetic semicond.)

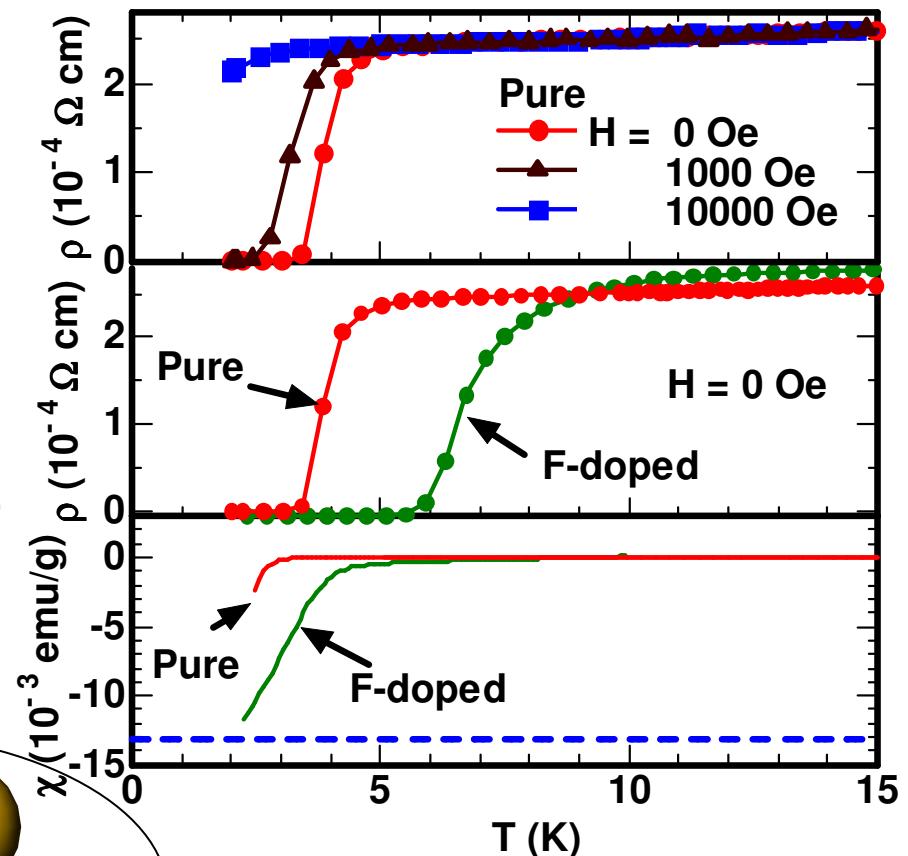
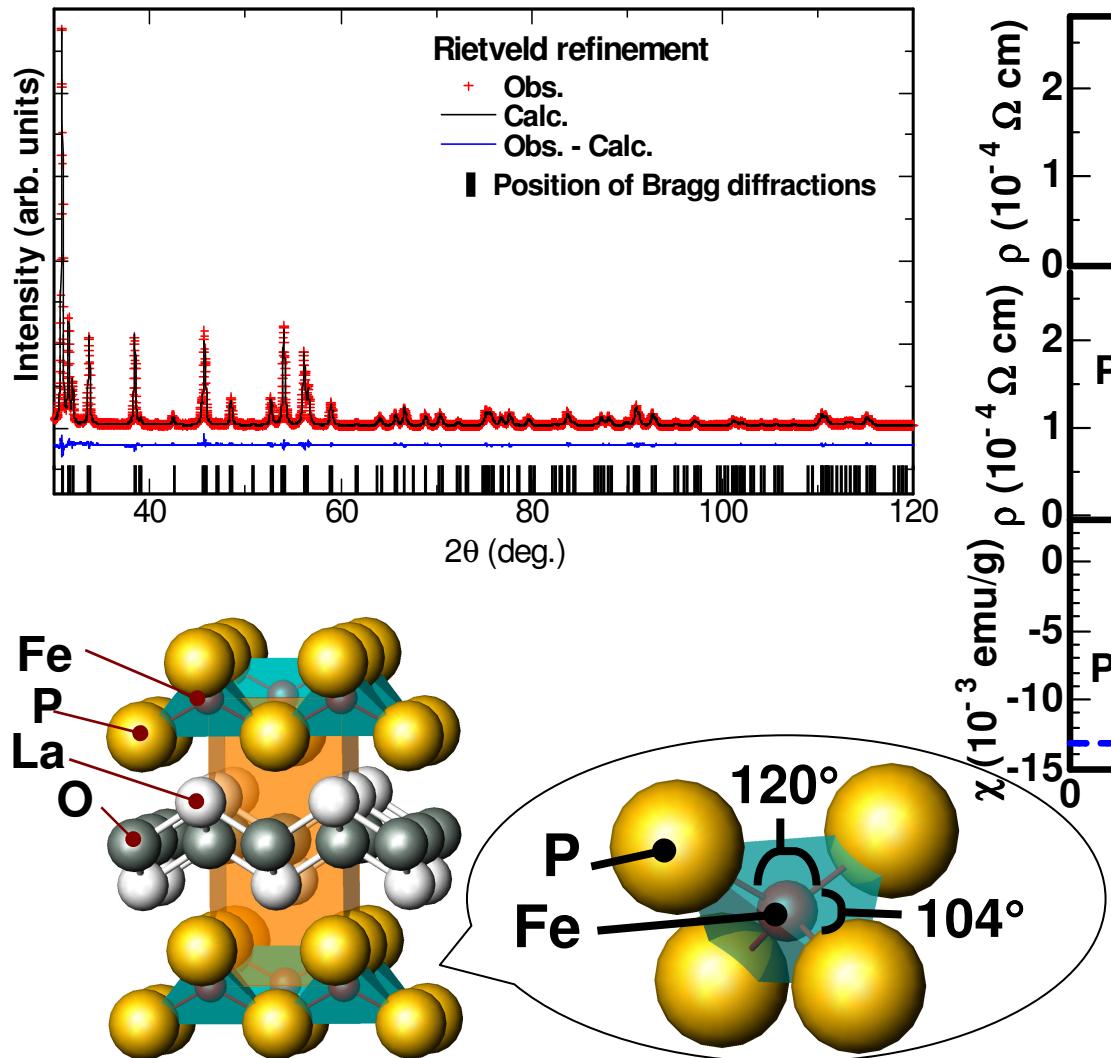


Properties of LaTMPnO

H																								
Li	Be																							
Na	Mg																							
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	P	As	S	Cl	Ar	He					

TM^{2+}	Mn(3d ⁵)		Fe(3d ⁶)		Co(3d ⁷)		Ni(3d ⁸)		(Cu)	Zn(3d ¹⁰)
Pn	P	As	P	As	P	As	P	As	P	As
Elect. Prop.	Semiconductor			Super-conductor	Metal		Super-conductor		—	Semiconductor
Magnetism	AFM		conductor		FM		conductor		—	nonmagnetic
E_g	~1 eV		—		—		—		—	~1.5 eV
T_C / T_N	> 400 K	Undoped: 5 K	Undoped: X F-doped: 26 K	43 K	66 K	Undoped: 3 K	Undoped: 2.4 K			—
Ref.	Yanagi et al. JAP submitted	Kamihara et al. JACS(2006), Kamihara et al. JACS (2008)		Yanagi et al. PRB (2008)	Watanabe et al. IC (2007), Watanabe et al. JSSC (in press)		—		Kayanuma et al. PRB (2007), Kayanuma et al. TSF (2008)	

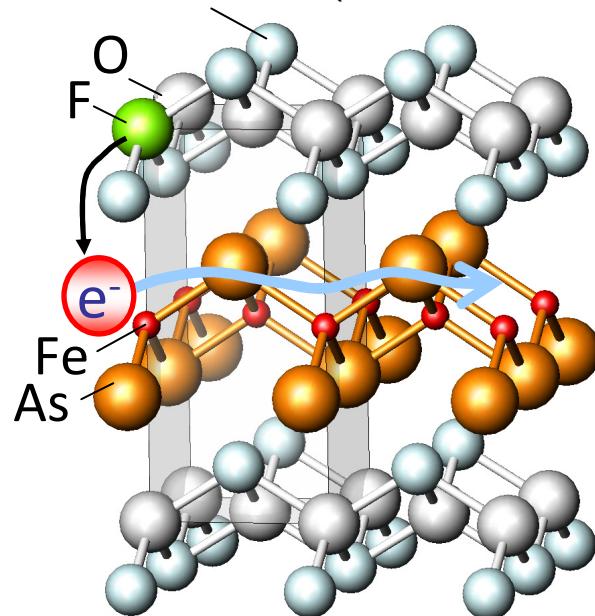
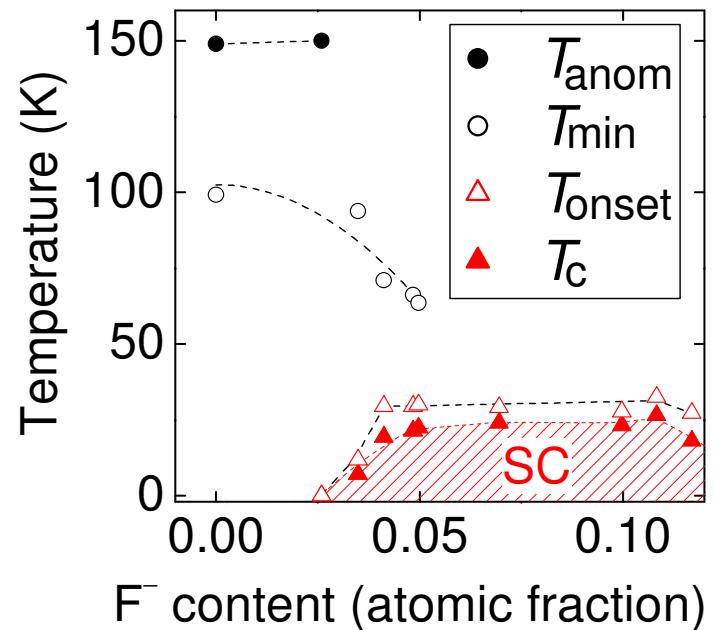
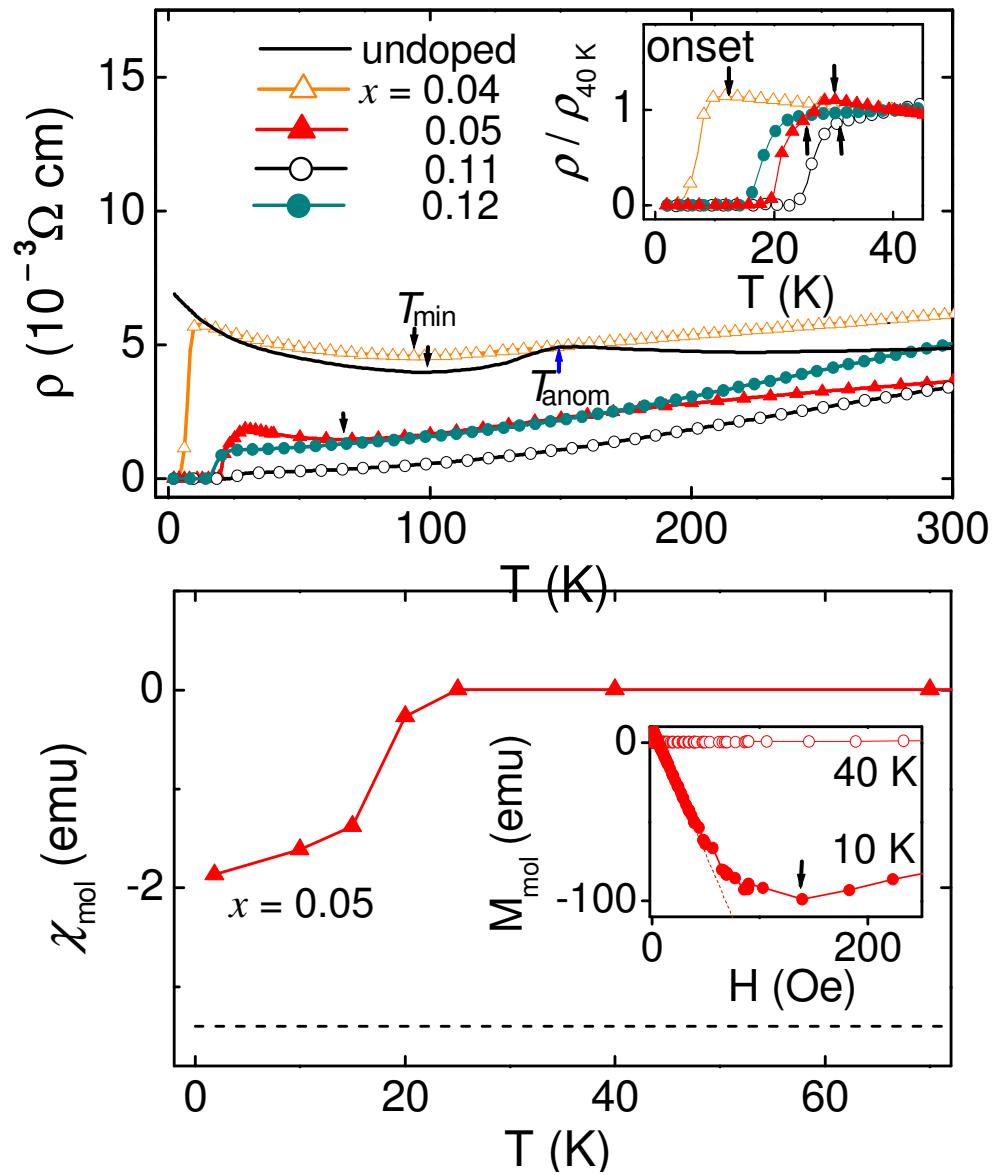
Discovery of Tc in LaFePO



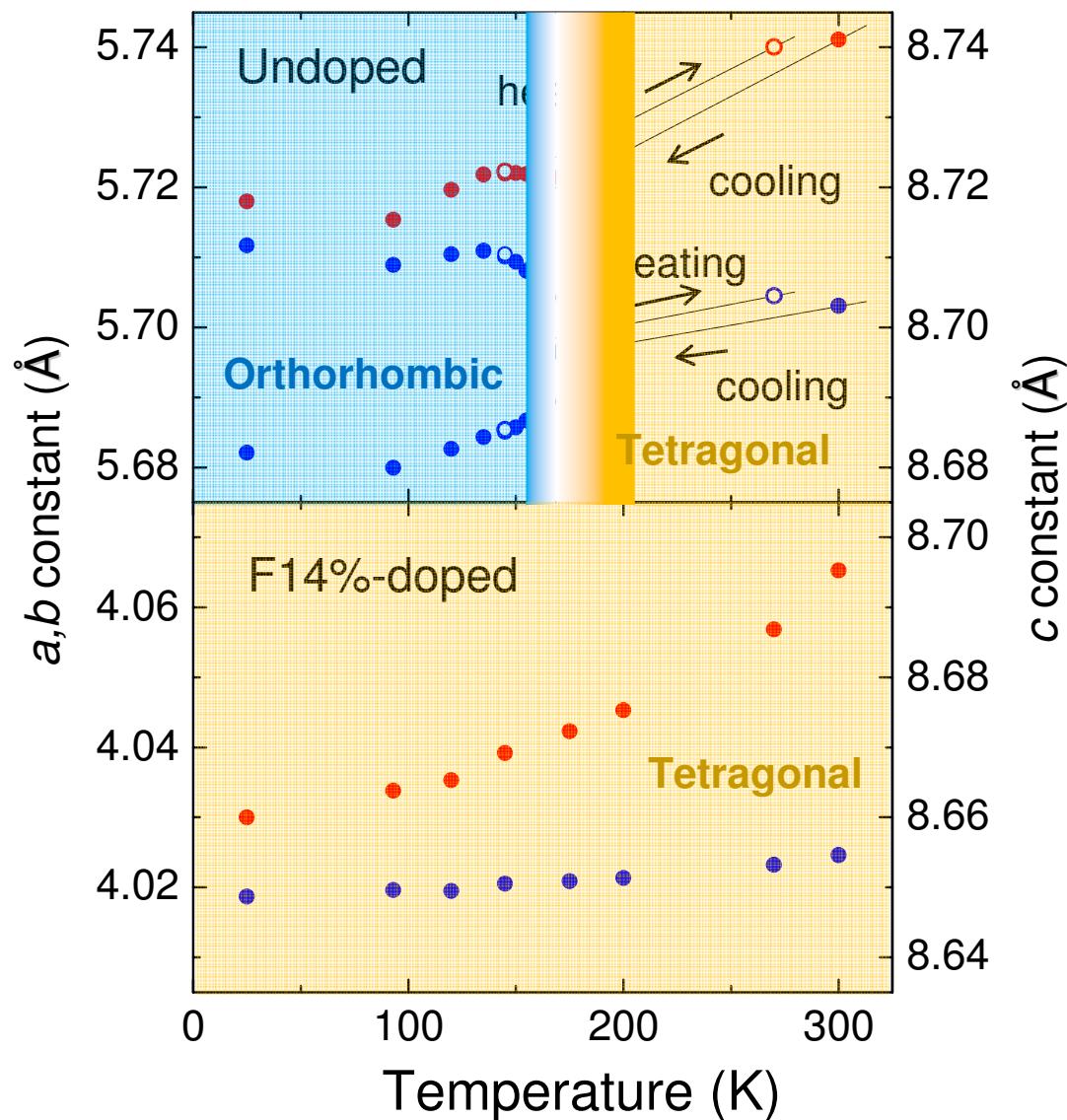
JACS, 128, 10012(2006)

F-doped LaFeAsO

published on-line in JACS (2008) on Feb 23

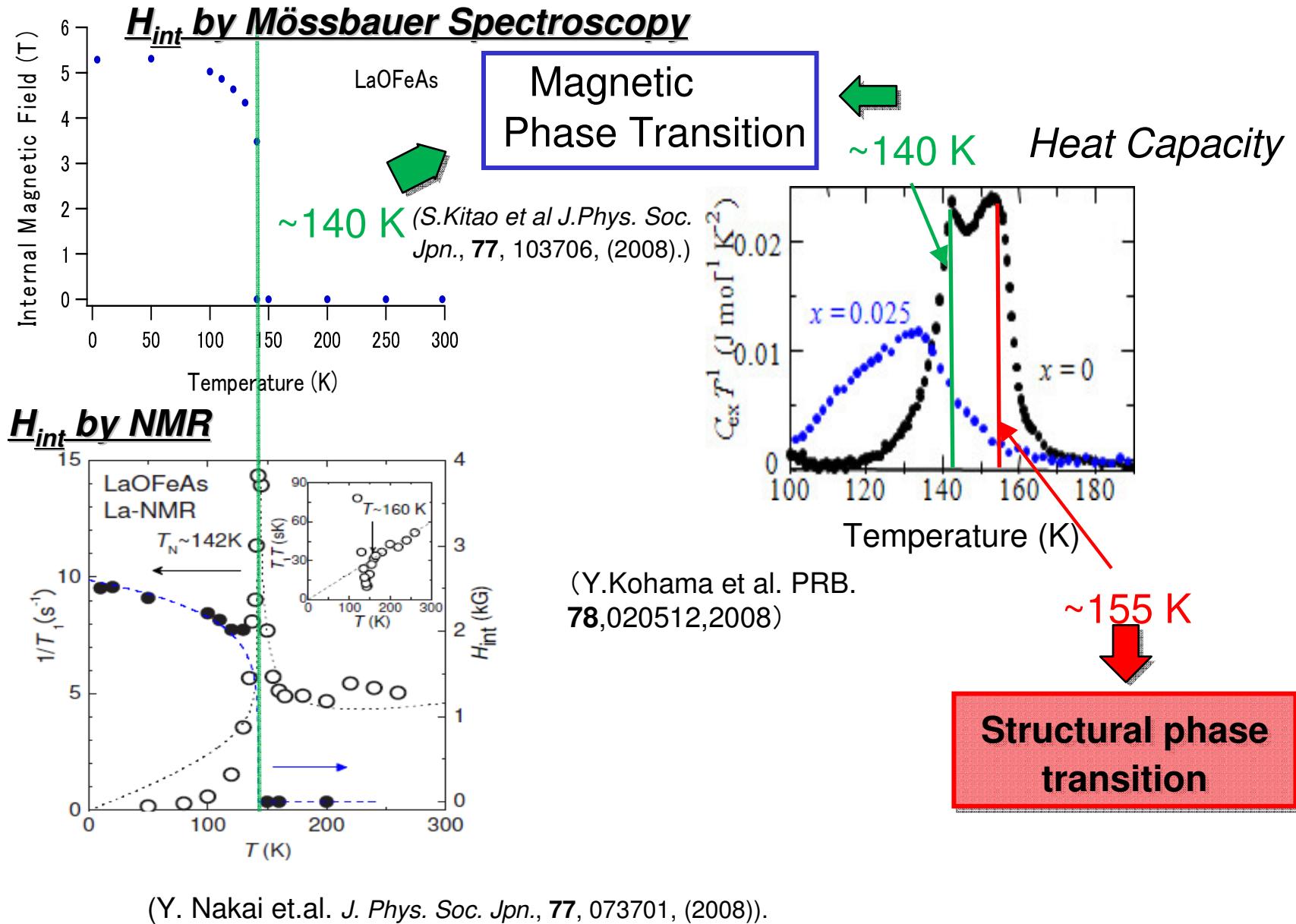


Lattice constant vs. T

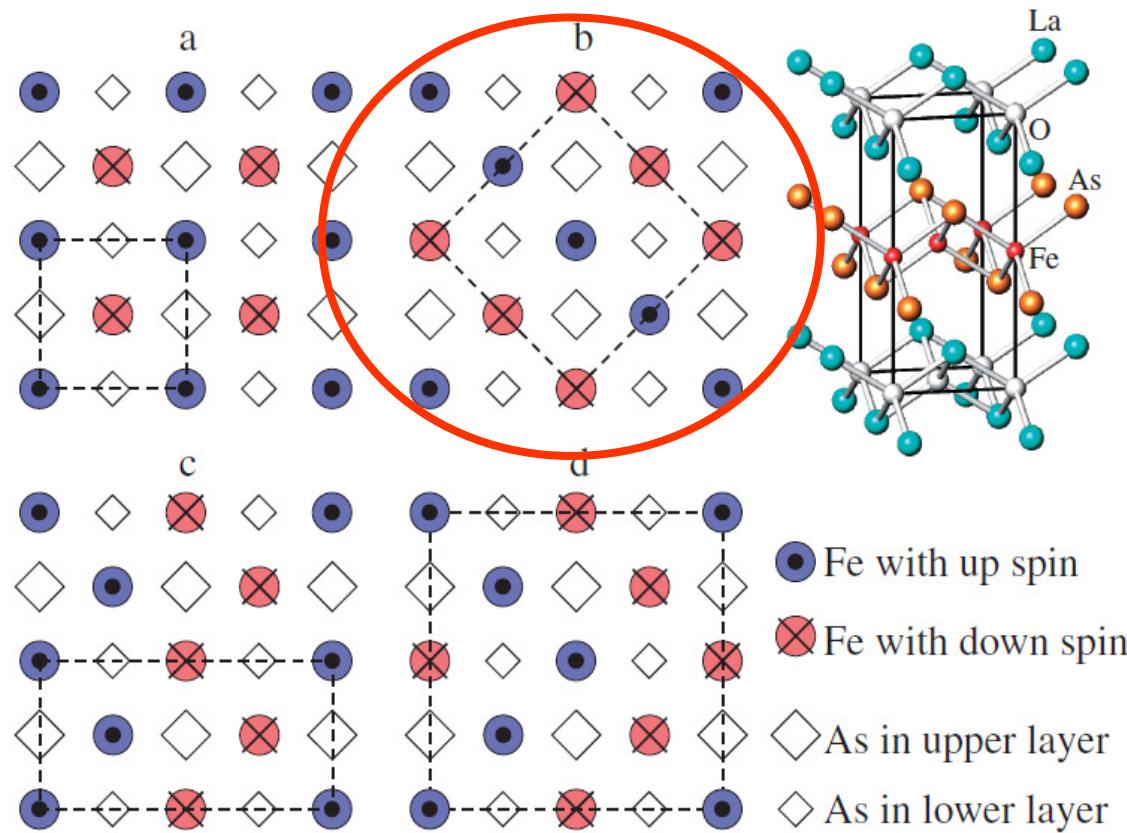


- a, b lattice constants drastically separate at ~ 160 K.
- $\sim 0.5\%$ difference between a and b @ 120 K.
- F-doping keeps the tetragonal symmetry down to 25 K.

What happens at ~150K?



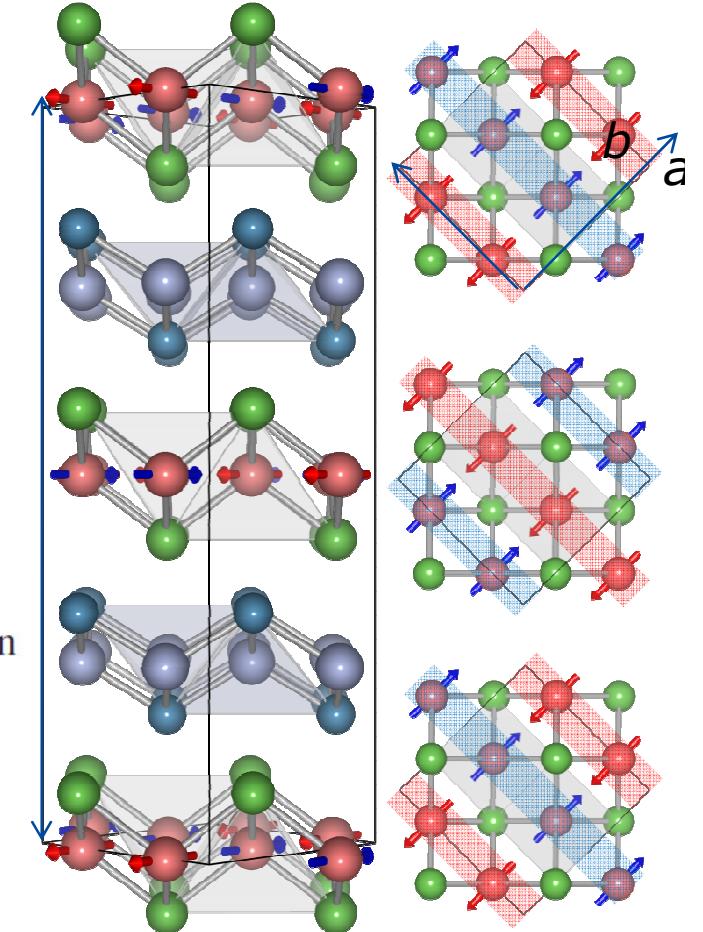
Most stable magnetic ordering in ortho-phase



Most stable AF-phase (stripe-type)

Magnetic moment/Fe = $2\mu_B$

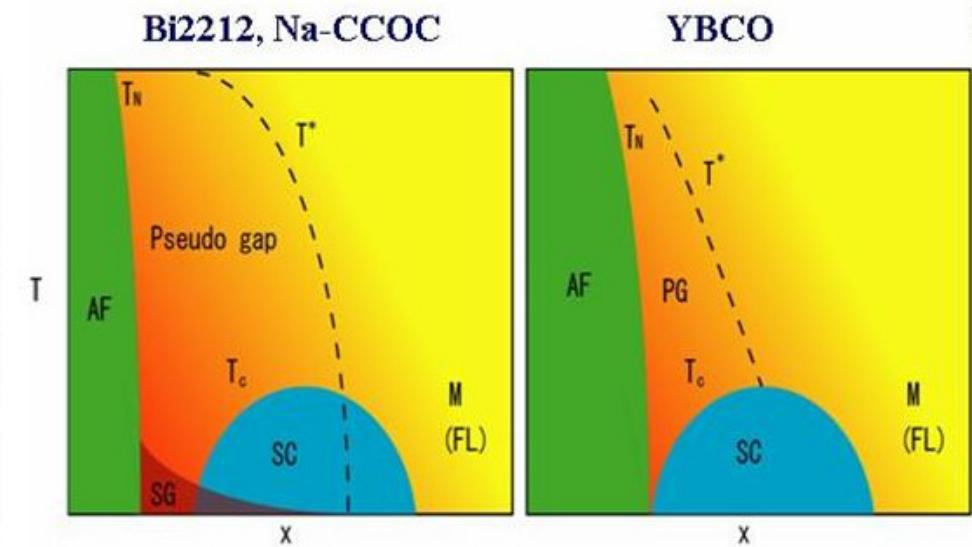
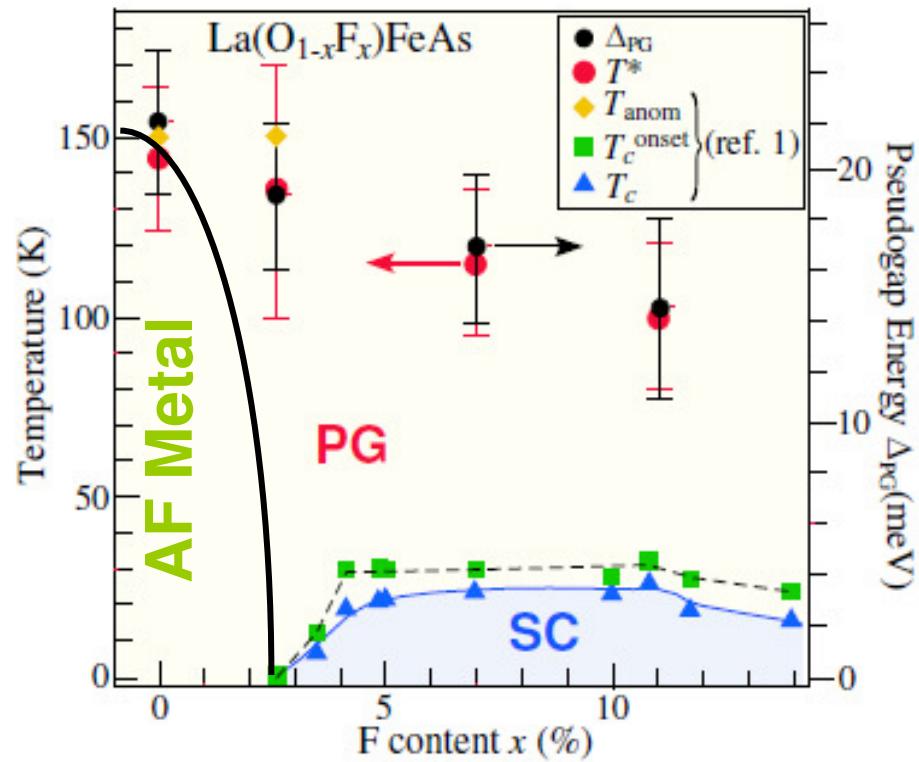
Ishibashi, Terakura, Hosono, JPSJ, 77, 053709 (2008).



$0.4\mu_B/\text{Fe}$

PRB(2008)

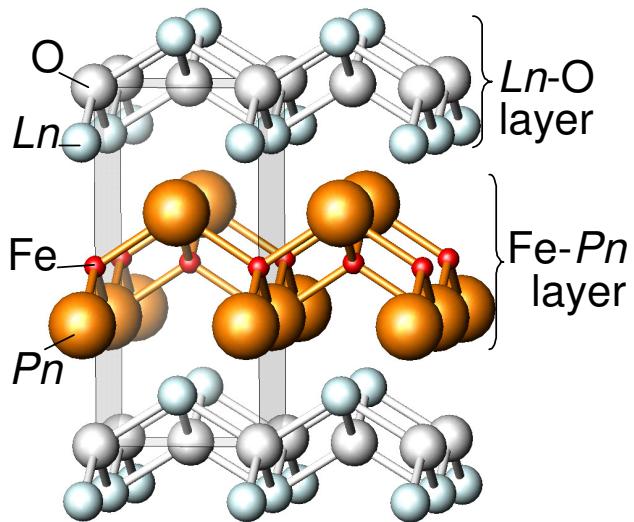
Phase Diagram: A close similarity to Cuprates



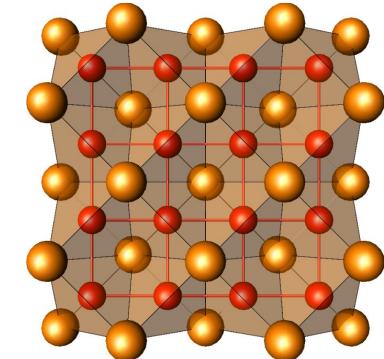
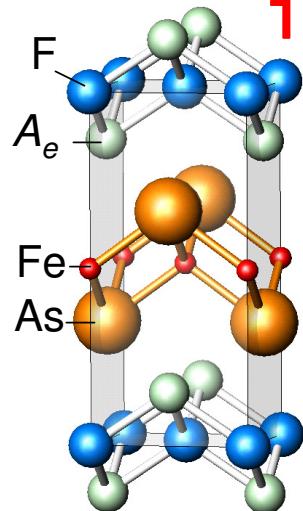
The presence of Pseudo-Gap was observed by PE (Takahashi G, Tohoku U. + Shin G, Tokyo U. + Hosono G. TIT)

Crystal Structures for Fe-based Superconductors

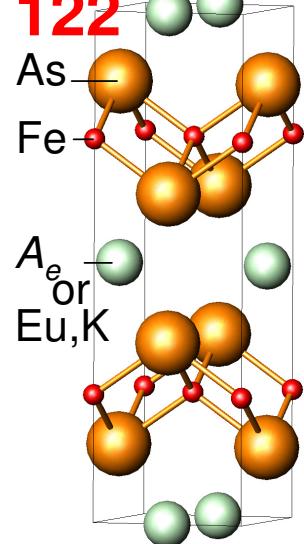
1111–LnO



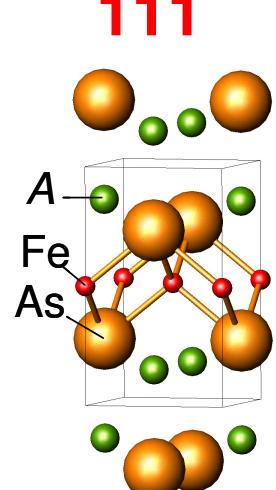
1111–AeF



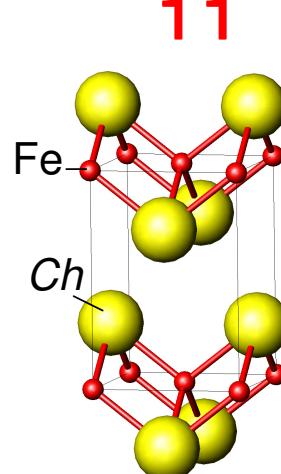
122



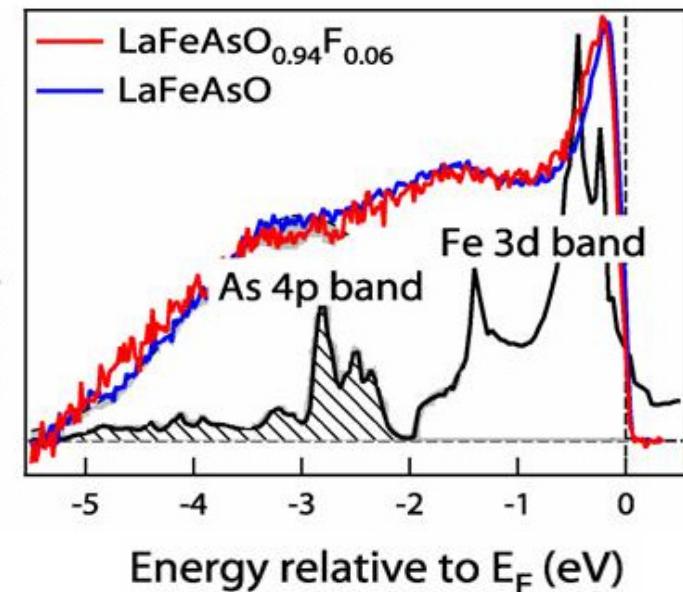
111



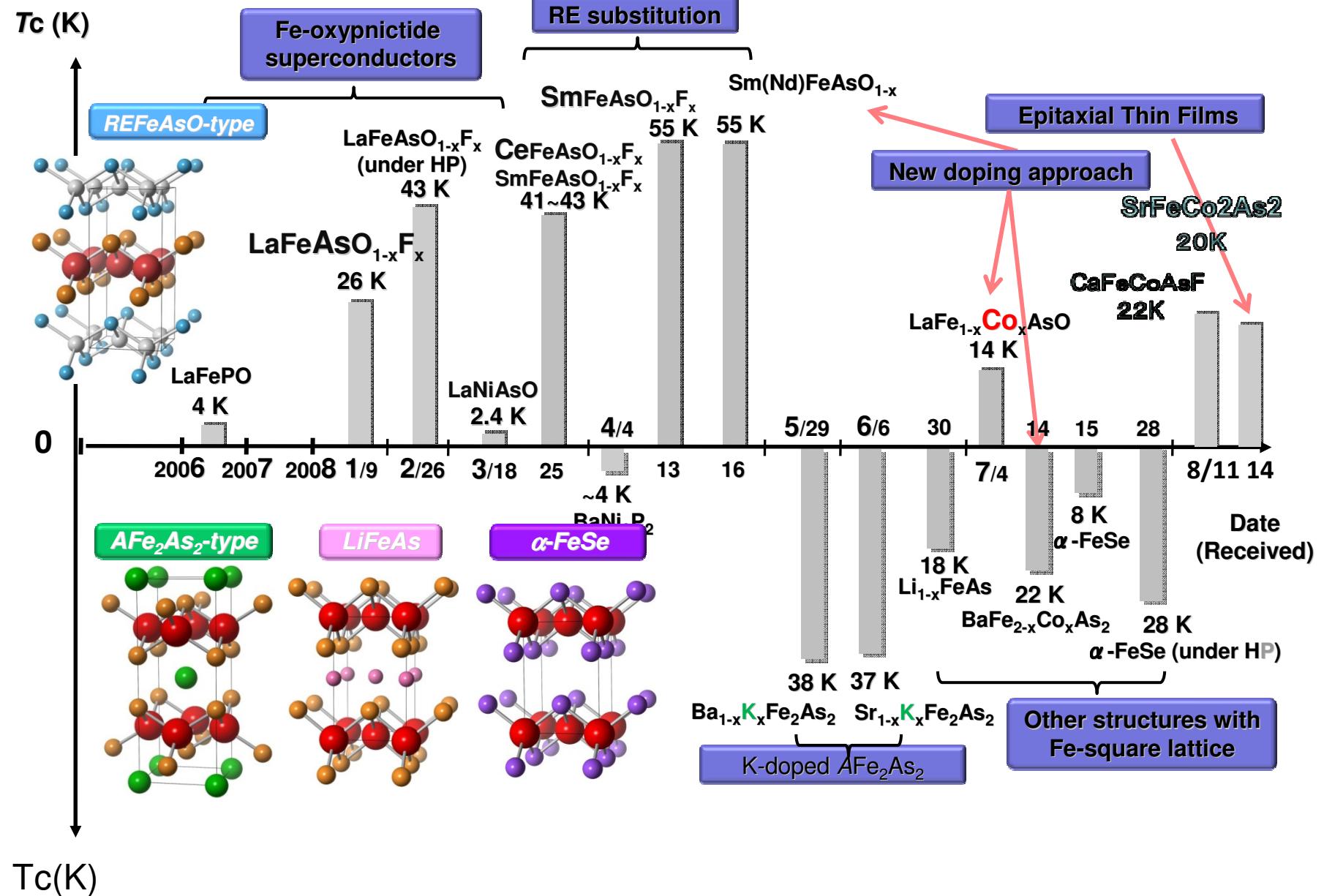
11



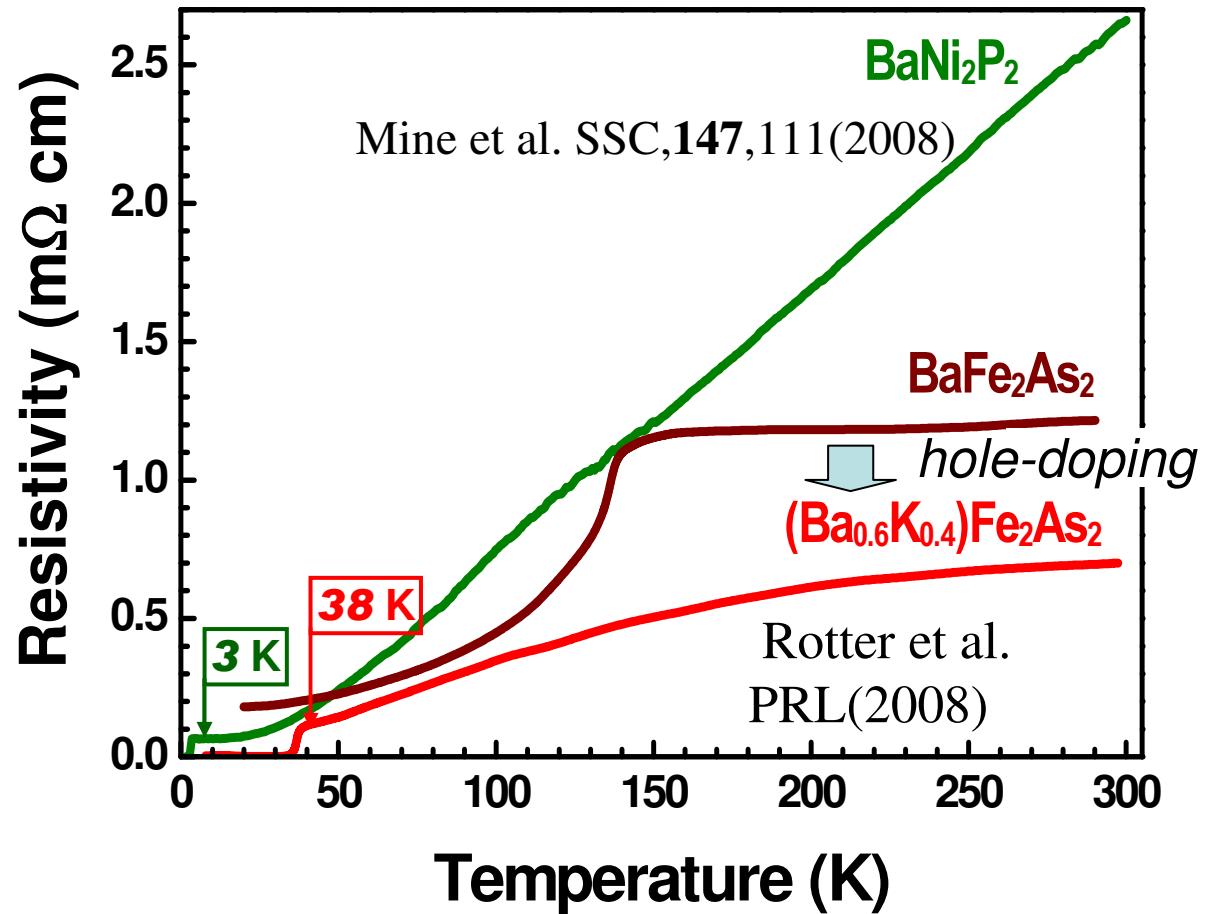
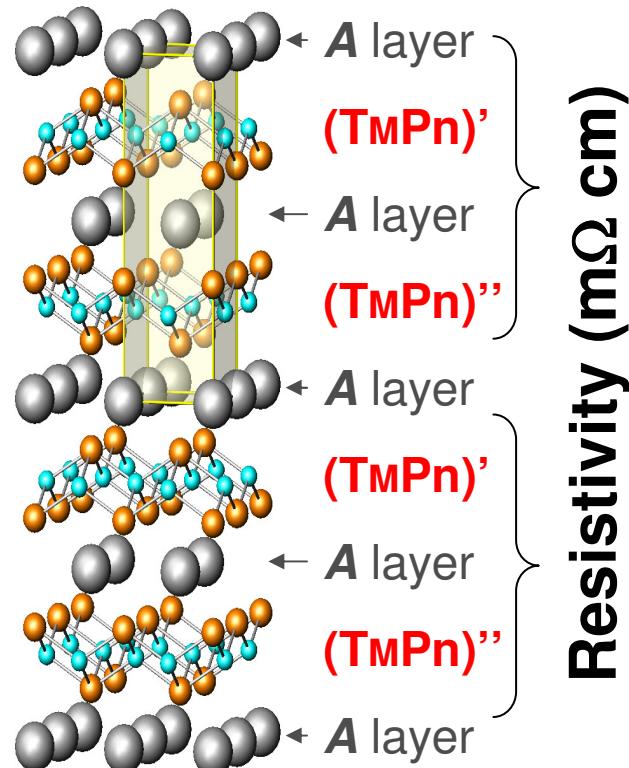
Intensity (arb. units)



Advances in superconductors with square Fe(Ni) lattice



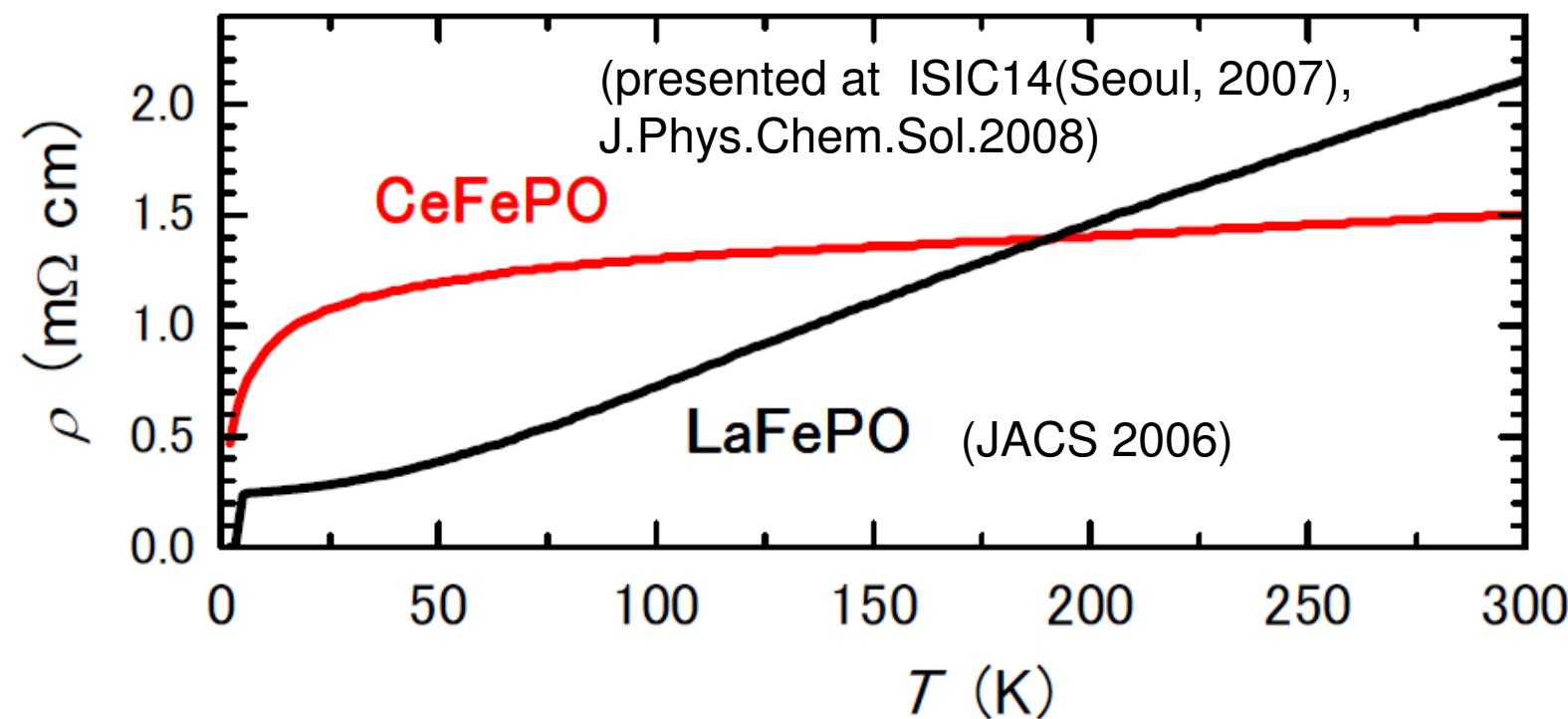
ATM_2Pn_2 : bi-layer structure



Structural (magnetic) phase transition at high temperature is required for high T_c .

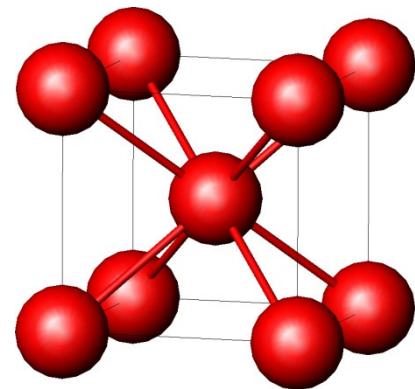
Why we skipped REFeAsO (RE= Ce,----)?

Heavy Fermion(Bruning et al PRL,2008)
 $\gamma = 700 \text{ mJmol}^{-1}\text{K}^{-2}$



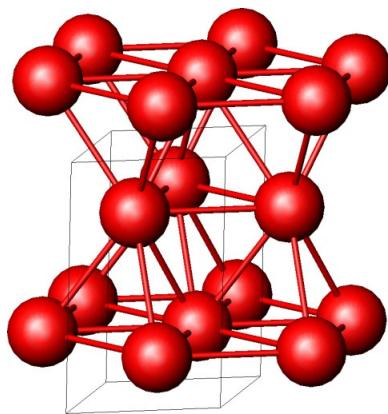
Carrier doping kills magnetism of Fe lattice

■ α -Fe (bcc)

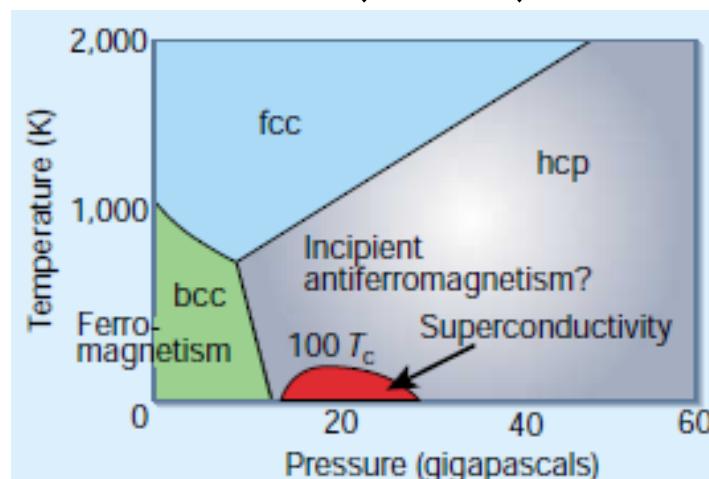


- Ferromagnetic Metal
- $d(\text{Fe-Fe}) \sim 0.248 \text{ nm}$

■ ε -Fe (hcp)

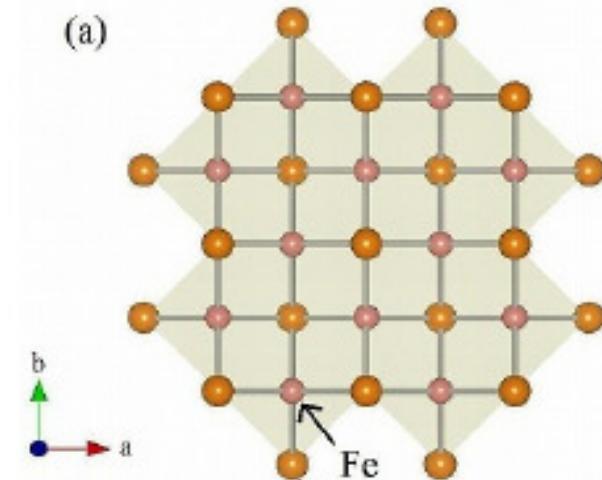


- Superconductors
(~20 GPa, $T_c < 2 \text{ K}$)
- $d(\text{Fe-Fe}) \sim 0.244 \text{ nm}$

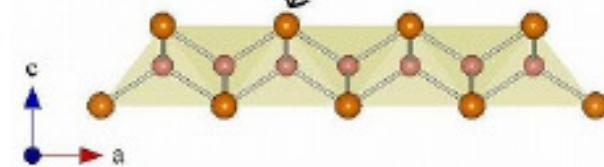


■ FeAs layer in ReFeAsO

(a)



(b)

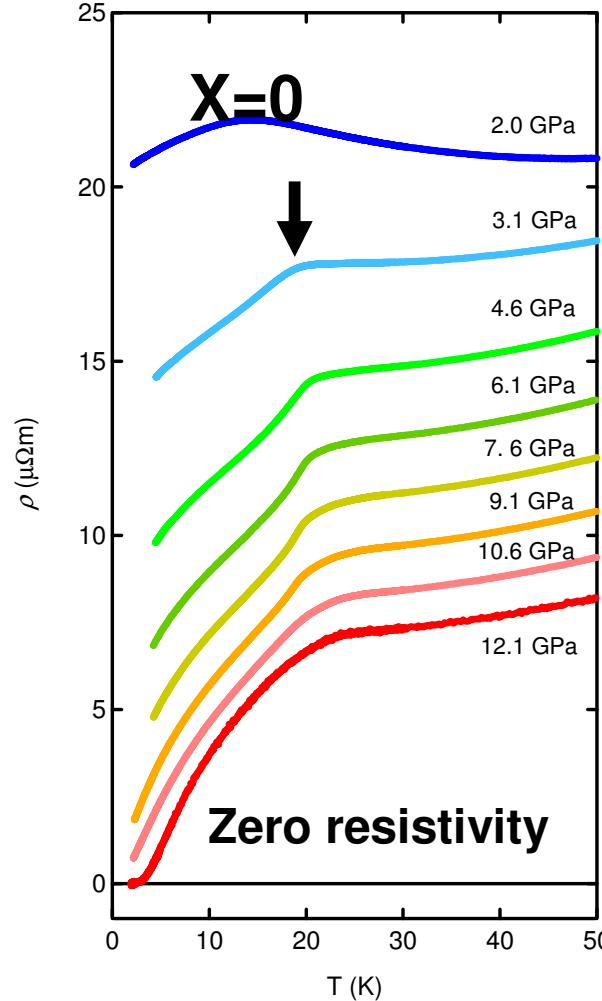


- Superconductors
(Ambient P, $T_c > 26 \text{ K}$)
- $d(\text{Fe-Fe}) \sim 0.285 \text{ nm}$

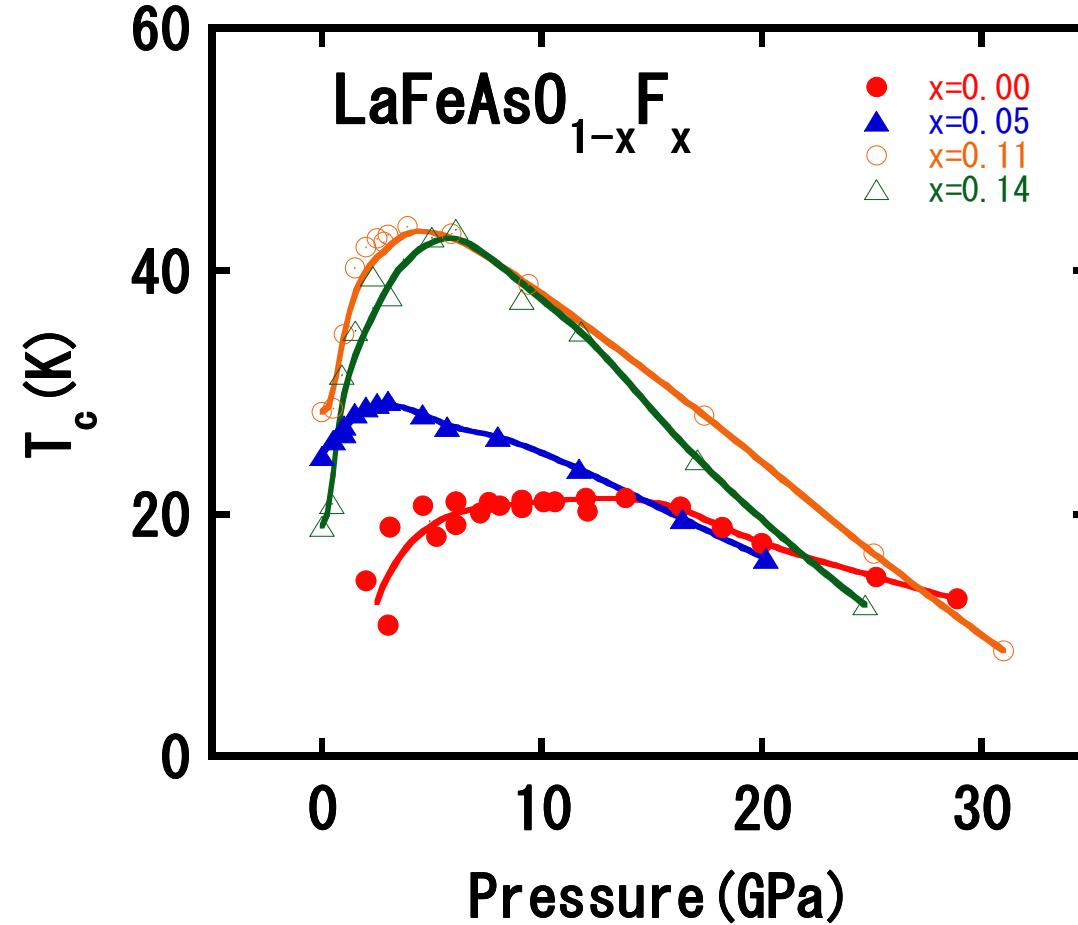
(Saxena et.al. *Nature*, 2001)

Tc-Pressure phase diagram

P-induced Tc in Parent material



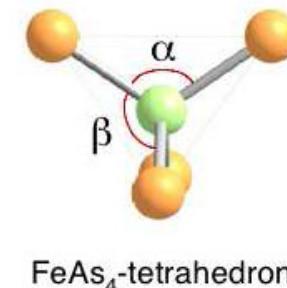
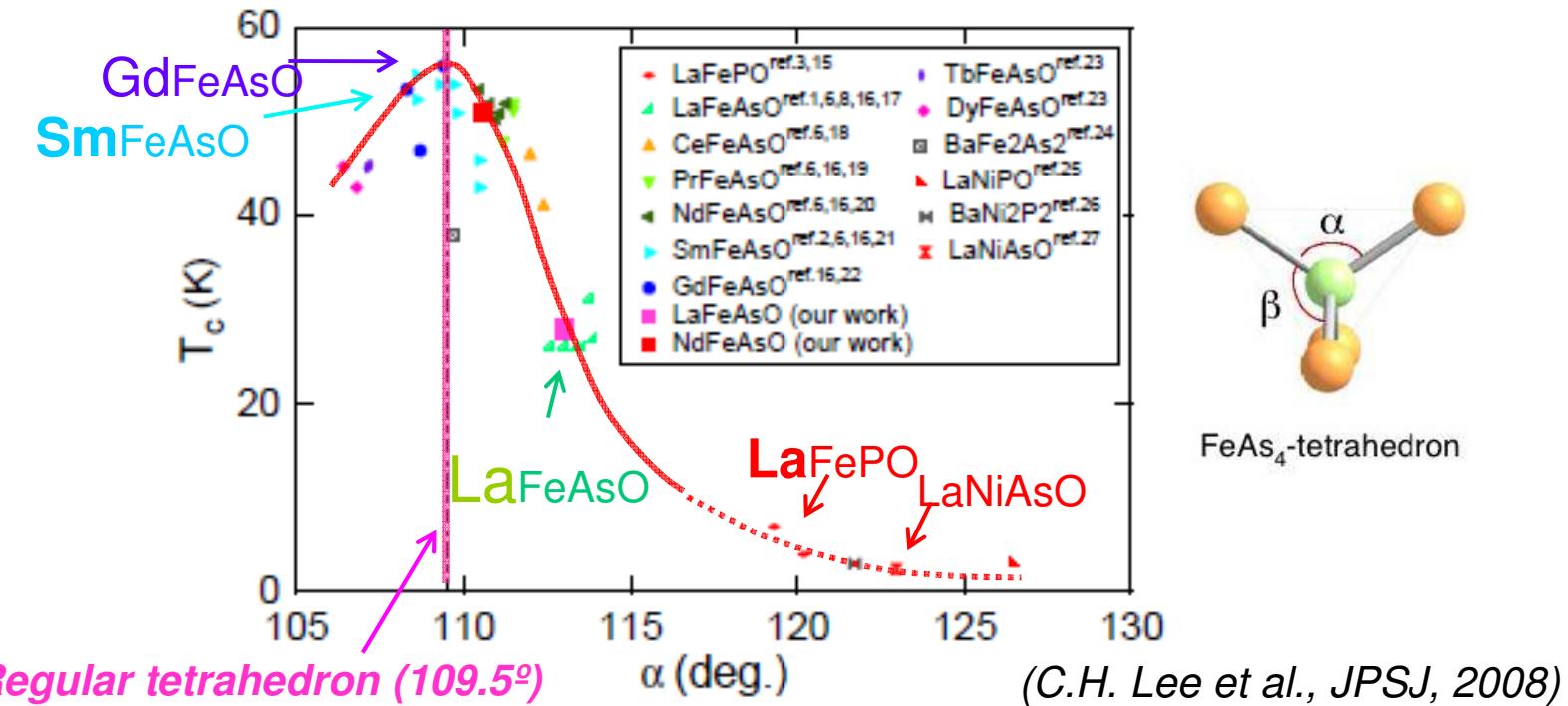
Okada et al (JPSJ 2009)



Takahashi Group (Nihon U.)+ Hosono G(TIT)
Nature 453, 376(2008)

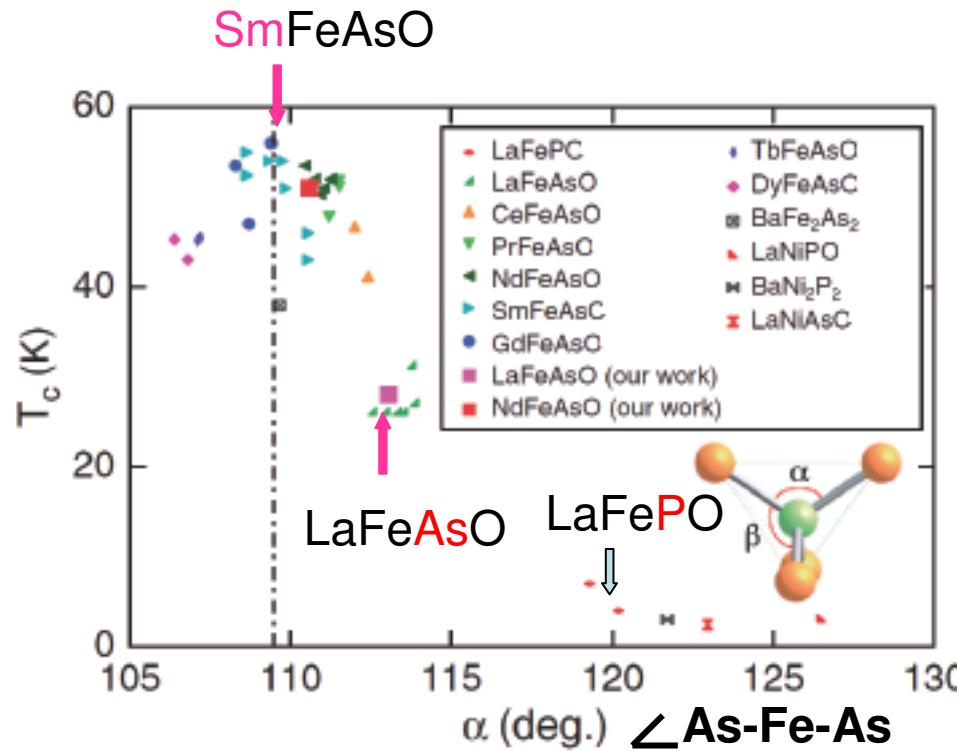
Local structure and Tc

Tc vs α (As-Fe-As angle)

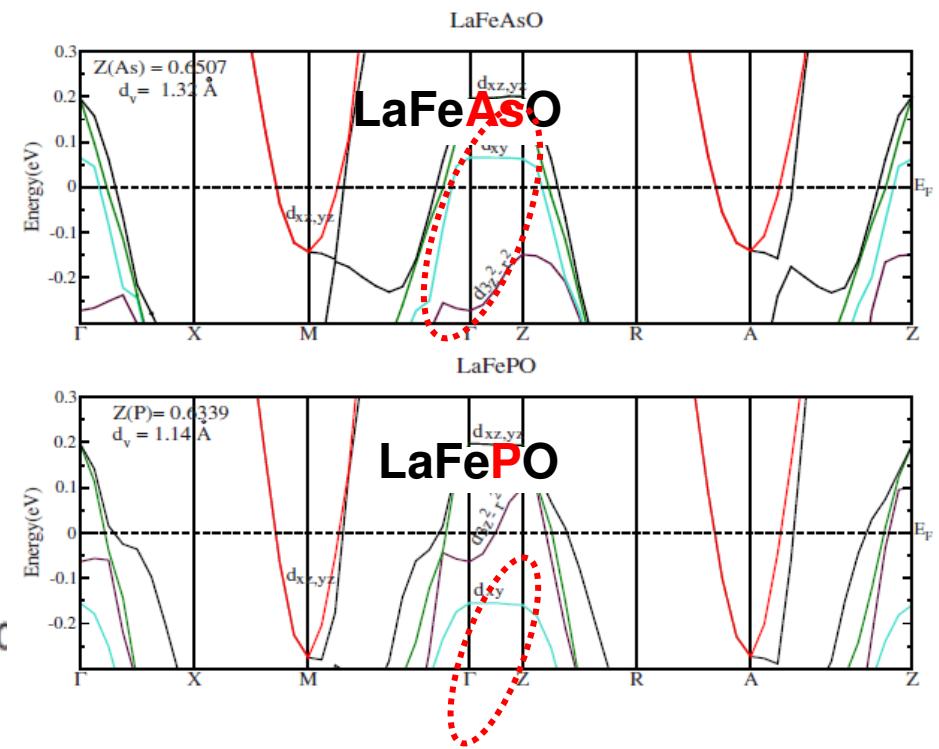


Higher symmetry of FeAs_4 tetrahedron leads to higher T_c in $Ln\text{FeAsO}$ system.

Local Structure and T_c



Lee et al.(JPSJ 2008)



$d_{x^2-y^2}$ and d_{xy} are shifted

New Fe-1111 member AeFeAsF ($\text{Ae} = \text{Ca} \& \text{Sr}$)

Substitution of blocking layer

$[\text{Ln}^{3+}\text{O}^{2-}]$ layer



Ln : rare-earth element
ex. La, Ce, Sm ... etc

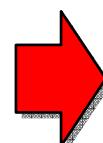
$[\text{Ae}^{2+}\text{F}^-]$ layer

Ae : alkali-earth element
ex. Ca, Sr

Doping method

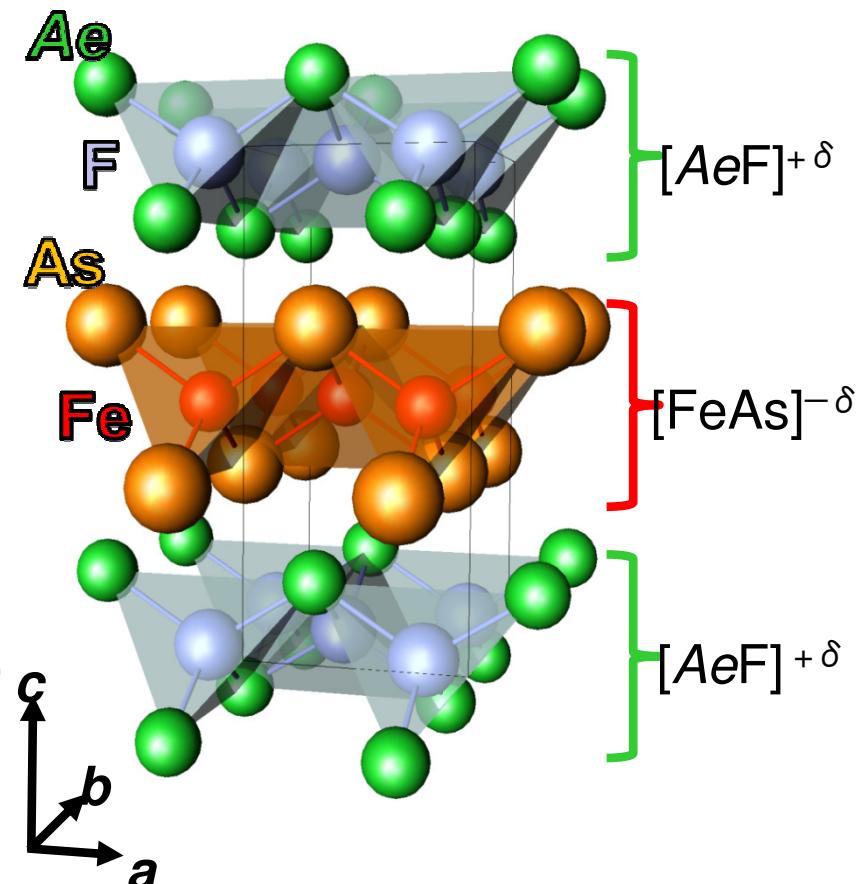
① Doping to AeF layer: $\text{Ae}, \text{F} \rightarrow ?$ \times

② Doping to FeAs layer: $\text{Fe} \rightarrow \text{Co}, \text{Ni}$



$\text{CaFe}_{1-x}\text{Co}_x\text{AsF}$ $T_c = \sim 22 \text{ K}$

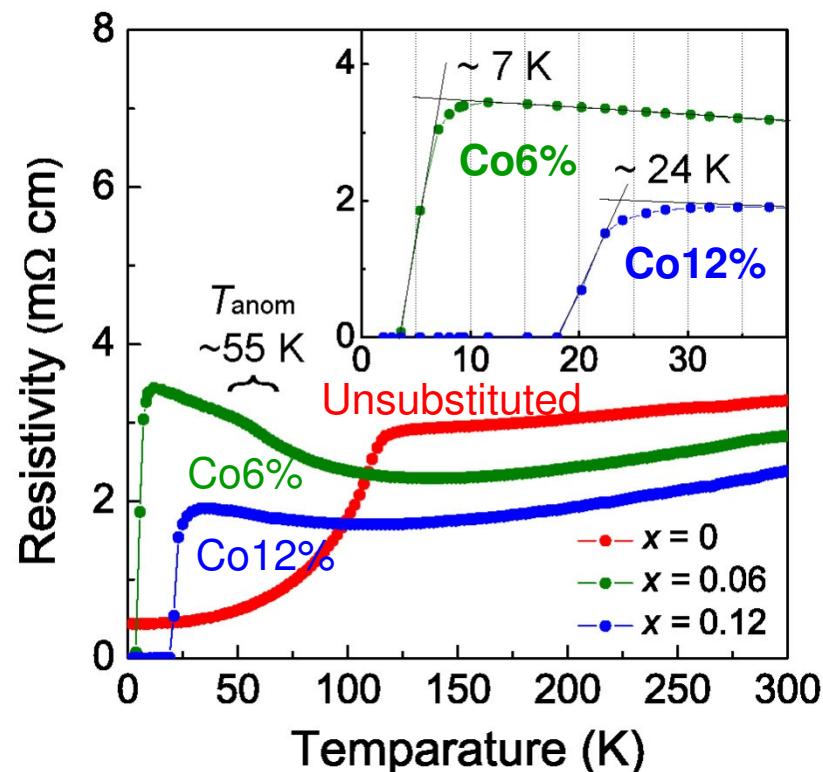
$\text{SrFe}_{1-x}\text{Co}_x\text{AsF}$ $T_c = \sim 4 \text{ K}$



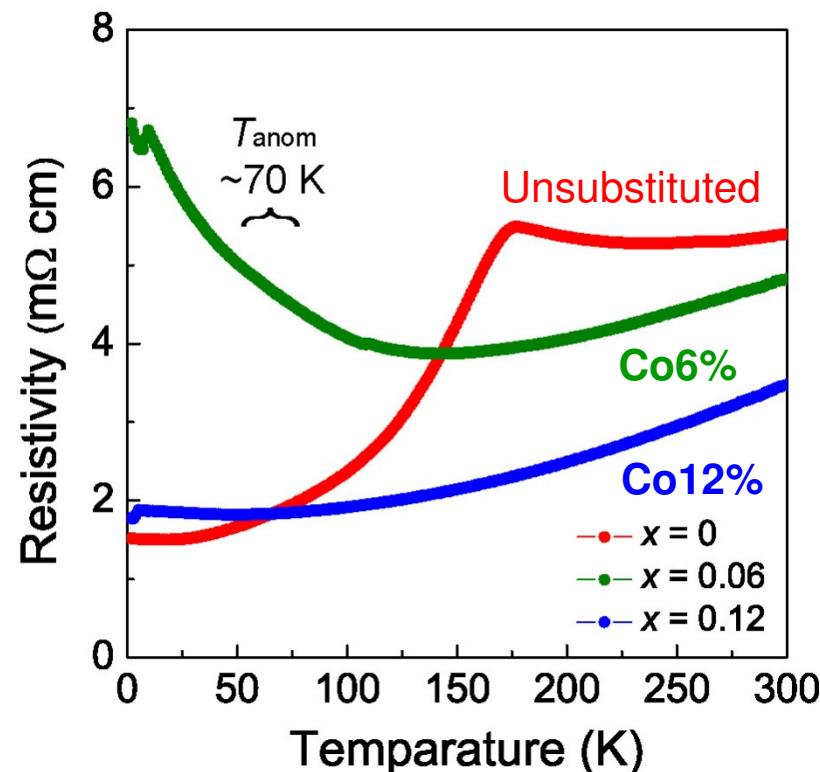
(Matsuishi et al., JACS, JPSJ(2008))

Superconductivity in $AeFe_{1-x}Co_xAsF$

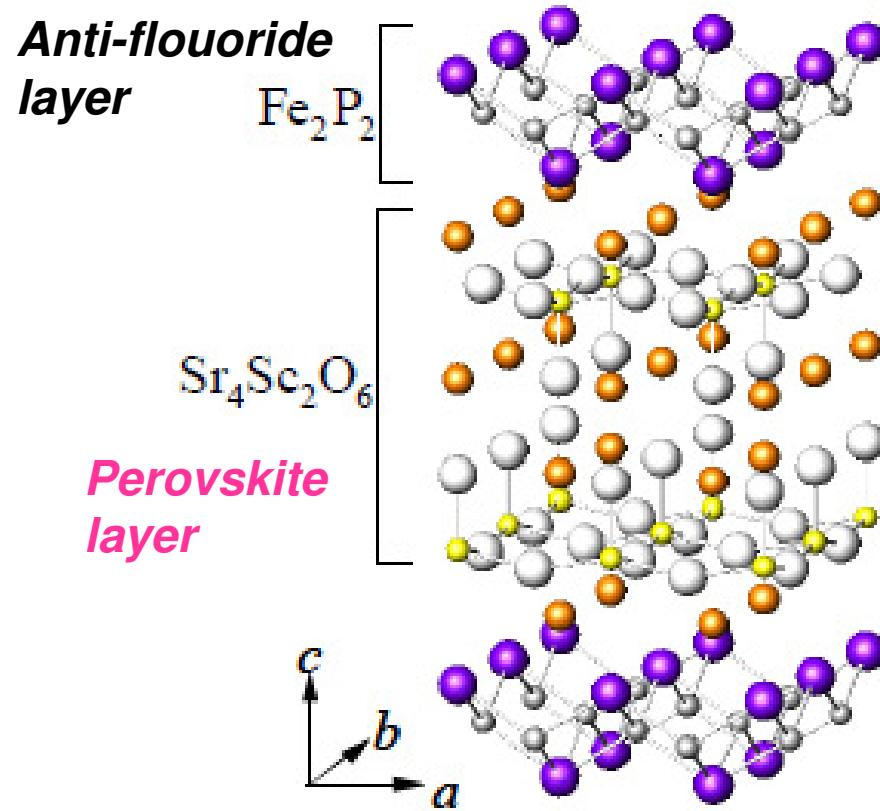
CaFeAsF



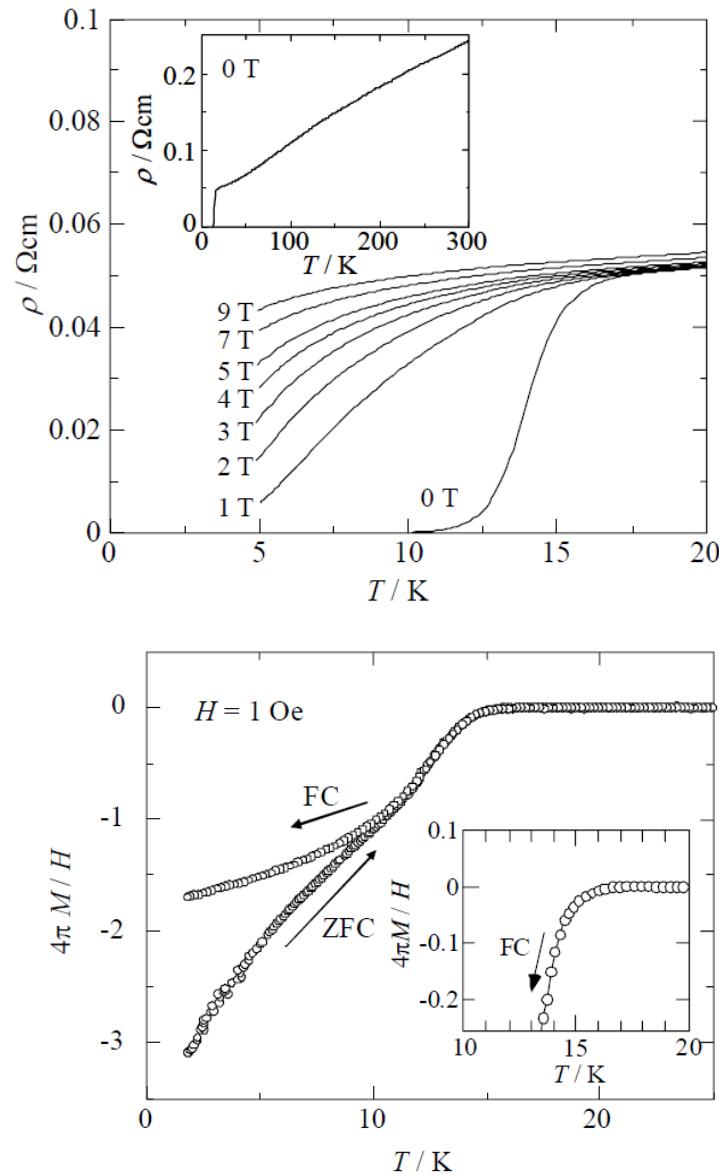
SrFeAsF



Perovskite-blocking layer



H.Ogino et al.
Presented at APS(March)

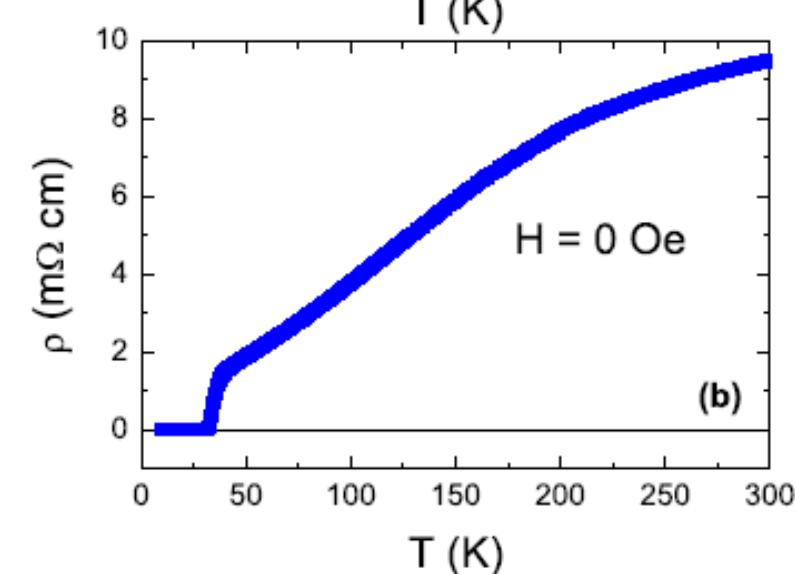
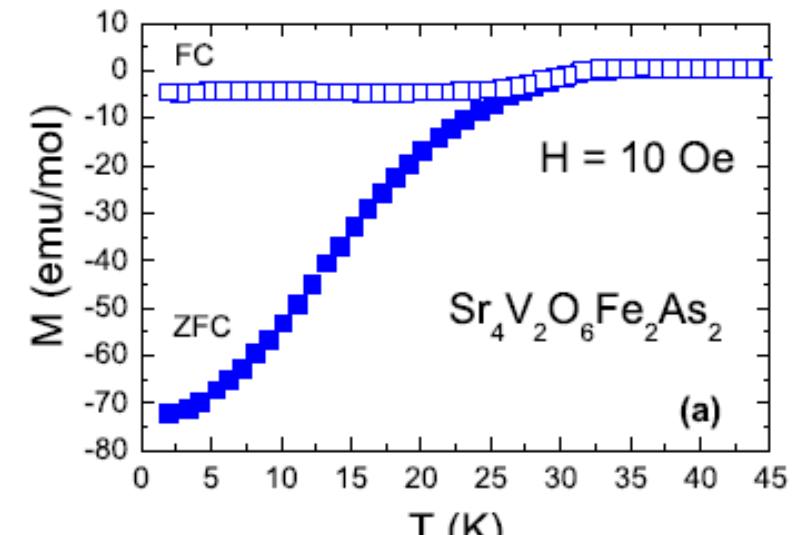
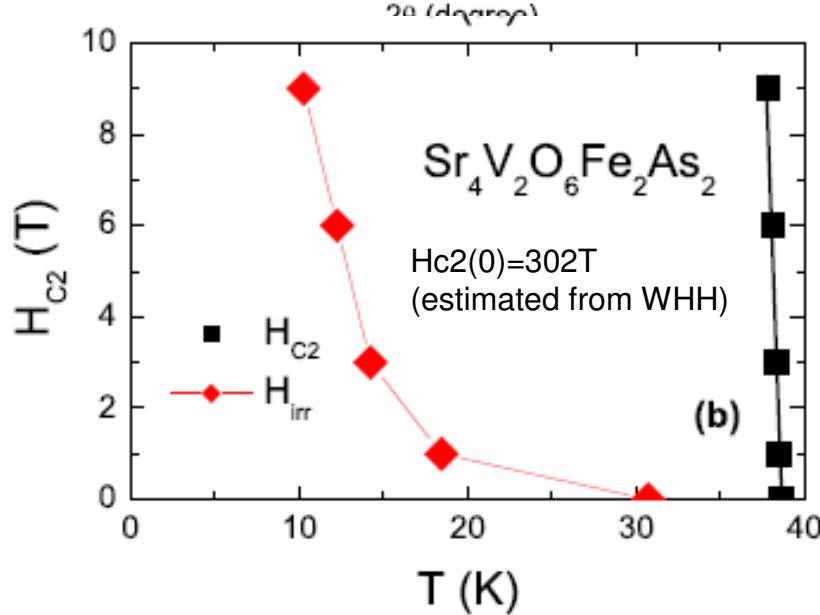
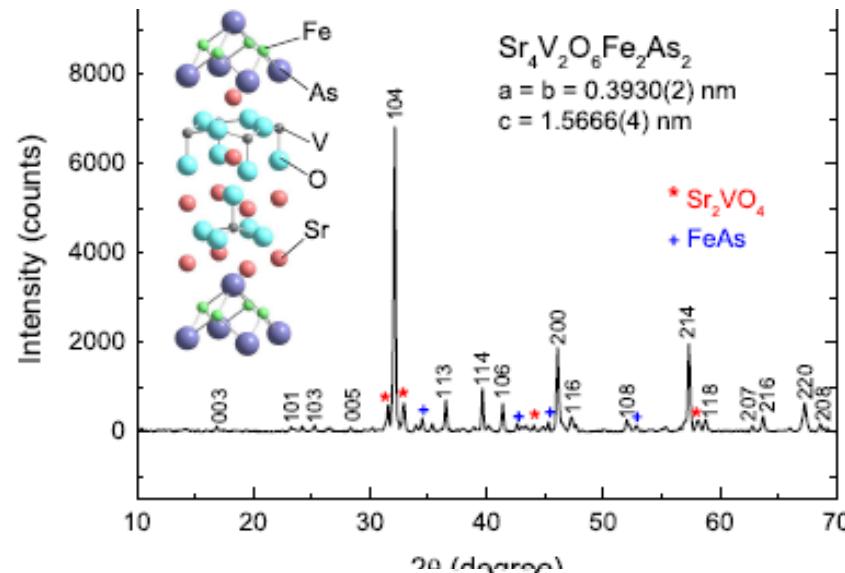


April 12, 2009

Superconductivity at 37.2 K in the Parent Phase $\text{Sr}_4\text{V}_2\text{O}_6\text{Fe}_2\text{As}_2$

Xiyu Zhu, Fei Han, Gang Mu, Peng Cheng, Bing Shen, Bin Zeng, and Hai-Hu Wen*

National Laboratory for Superconductivity, Institute of Physics and Beijing National Laboratory for Condensed Matter Physics,
Chinese Academy of Sciences, P. O. Box 603, Beijing 100190, China

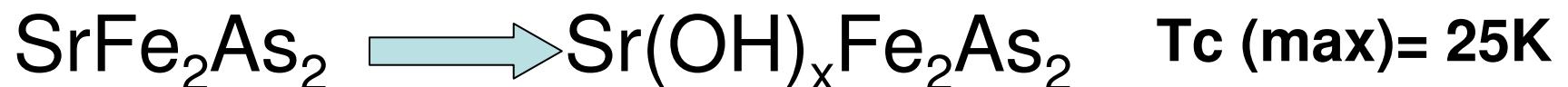


A Tentative Mechanism

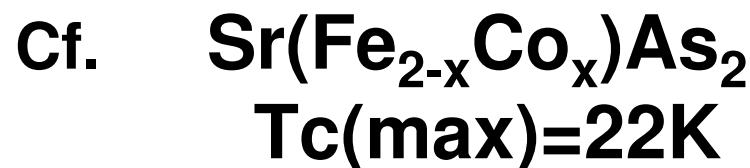
Intercalation

H_2O ($\sim 0.3\text{nm}$) is larger than Sr^{2+} (0.23nm)

OH^- is more plausible



Hole-doping to FeAs layer
via OH^- insertion to Sr-layer



Chemical doping with H_2O is possible in Sr122.

Comparison with Cuprates and MgB₂

	Fe-oxypnictides	MgB ₂	Cuprates
Parent Material	(bad) metal ($T_N \sim 150K$)	metal	Mott Insulator ($T_N \sim 400K$)
Fermi Level	3d 5-bands	2-bands	3d single band
Max T _c	56K	40K	~140K
Impurity effect	robust	sensitive	sensitive
Sc gap symmetry	extended-s-wave(?)	s-wave	d-wave
H _c ² (0)	100-200T>	~40T	~100T
J _c	?		

Contemporary superconducting materials

Chemical Communications 2005, 5373-5377.

By Bob Cava



Robert Cava is Chair of the Department of Chemistry at Princeton and a Professor in Chemistry and Materials. He is a Fellow of the American Physical Society and the American Ceramic Society, and a member of the US National Academy of Sciences. He was Acting Director of the Princeton Materials Institute from 2001 to 2002. He began at Princeton in 1997 after working at Bell Laboratories from 1979 to 1997, where he was a Distinguished Member of Technical Staff. He was a National Research Council Postdoctoral Fellow at NIST from 1978 to 1979 after receiving his Ph.D. in Ceramics from MIT in 1978.

New superconductors are currently being discovered at 2-4 per year.

The search for new superconductors has largely been *the domain of condensed matter physicists* knowledgeable in the synthesis of intermetallic or oxide compounds. *Chemists have much to offer the field*, and have also found new superconductors, both in focused searches and by accident in the synthetic programs with other goal.

Journey for discovering a new continent

Frontier to Transparent Oxide Semiconductors

